S-191ExxxxA Series

AUTOMOTIVE, 125°C OPERATION, 36 V, WINDOW VOLTAGE DETECTOR WITH SENSE PIN REVERSE CONNECTION PROTECTION

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This IC, developed using CMOS technology, is a high-accuracy window voltage detector that detects undervoltage and overvoltage. The detection voltage and release voltage are fixed internally with an accuracy of ±1.5%.
Apart from the power supply pin, the detection voltage input pin (SENSE pin) is also prepared, so the output is stable even if the SENSE pin voltage (V_{SENSE}) falls to 0 V. The SENSE pin also has a built-in reverse connection protection circuit that reduces current in the SENSE pin during a reverse connection.
The release signal can be delayed by setting a capacitor externally, and the release delay time accuracy is ±15% (C_D = 3.3 nF). The output form is Nch open-drain output.

ABLIC Inc. offers FIT rate calculated based on actual customer usage conditions in order to support customer functional safety design.
For more information regarding our FIT rate calculation, contact our sales representatives.

Caution **This product can be used in vehicle equipment and in-vehicle equipment. Before using the product for these purposes, it is imperative to contact our sales representatives.**

■ Features

- Detection voltage: Undervoltage detection voltage 4.0 V to 10.0 V (0.05 V step); Overvoltage detection voltage 16.0 V to 18.0 V (0.1 V step)
- Detection voltage accuracy: Undervoltage detection voltage ±1.5%; Overvoltage detection voltage ±1.5%
- Hysteresis width selectable from "Available" / "Unavailable": "Available": 5.0%, 10.0%; "Unavailable": 0%
- Release delay time accuracy: ±15% (C_D = 3.3 nF)
- Current consumption: 0.9 µA typ.
- Output form: Nch open-drain output
- Built-in reverse connection protection circuit: Reduces current in the SENSE pin during a reverse connection.
- Operation voltage range: 3.0 V to 36.0 V
- Operation temperature range: Ta = −40°C to +125°C
- Lead-free (Sn 100%), halogen-free
- Withstand 45 V load dump
- AEC-Q100 qualified*1

***1.** Contact our sales representatives for details.

■ Applications

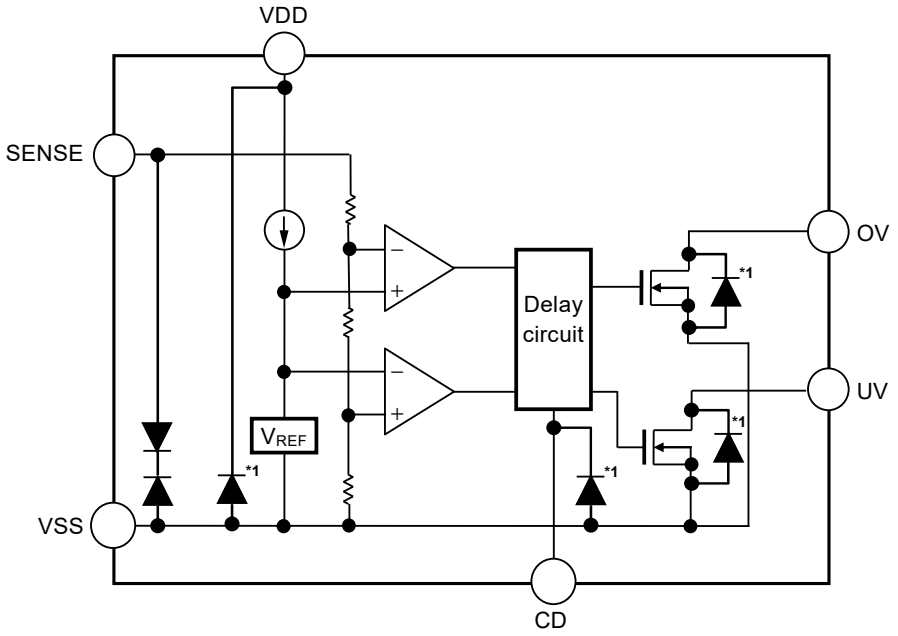
- Overvoltage detection of power supply for automotive electric component
- Automotive battery voltage detection
- For automotive use (engine, transmission, suspension, ABS, related-devices for EV / HEV / PHEV, etc.)

■ Packages

- HTMSOP-8
- HSNT-8(2030)

■ Block Diagrams

1. S-191E Series L type

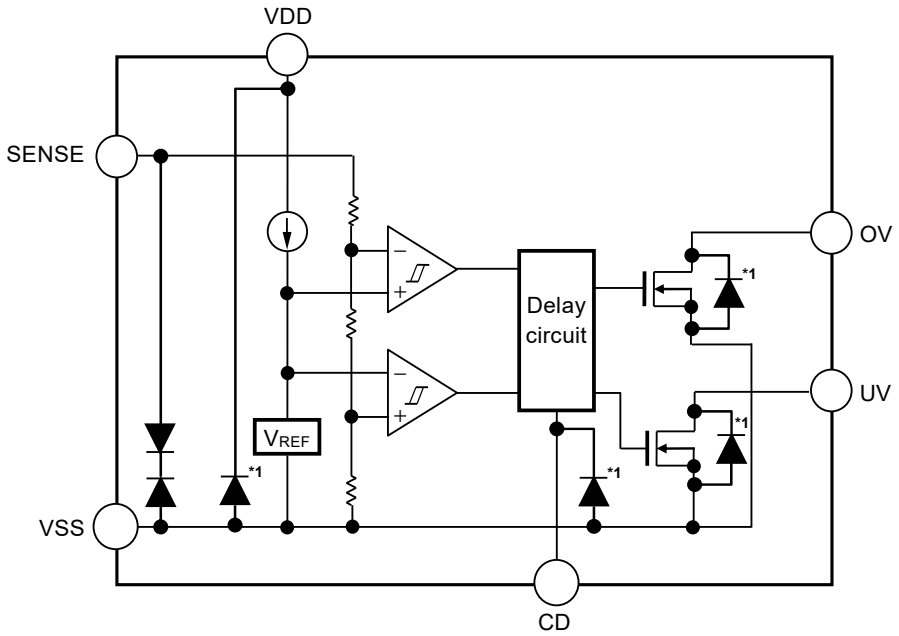


***1.** Parasitic diode

Figure 1

Product Type	Hysteresis Width (V_{UVHYS}, V_{OVHYS})	UV, OV Pin Output Form	UV, OV Pin Output Logic
L type	0%	Nch open-drain output	Active "L"

2. S-191E Series M / N type



1. Parasitic diode

Figure 2

Product Type	Hysteresis Width (V_{UVHYS}, V_{OVHYS})	UV, OV Pin Output Form	UV, OV Pin Output Logic
M type	5.0%	Nch open-drain output	Active "L"
N type	10.0%	Nch open-drain output	Active "L"

■ AEC-Q100 Qualified

This IC supports AEC-Q100 for operation temperature grade 1.
Contact our sales representatives for details of AEC-Q100 reliability specification.

■ Product Name Structure

1. Product name

S-191E x xx x A - xxxx U 7

- Environmental code
  - U: Lead-free (Sn 100%), halogen-free
- Package abbreviation and IC packing specifications*1
  - S8T1: HTMSOP-8, Tape
  - A8T1: HSNT-8(2030), Tape
- Operation temperature
  - A: Ta = –40°C to +125°C
- Overvoltage detection voltage*2
  - A to W
- Undervoltage detection voltage
  - 40 to A0
  - (e.g., when the undervoltage detection voltage is 4.0 V, it is expressed as 40. when the undervoltage detection voltage is 10.0 V, it is expressed as A0.)
- Product type*3

***1.** Refer to the tape drawing.
***2.** Refer to **Table 1** for the overvoltage detection voltage.
***3.** Refer to "**2. Function list of product types**".

Table 1

Overvoltage Detection Voltage	Symbol
16.0 V	A
16.1 V	B
16.2 V	C
16.3 V	D
16.4 V	E
16.5 V	F
16.6 V	G

Overvoltage Detection Voltage	Symbol
16.7 V	H
16.8 V	J
16.9 V	K
17.0 V	L
17.1 V	M
17.2 V	N
17.3 V	P

Overvoltage Detection Voltage	Symbol
17.4 V	Q
17.5 V	R
17.6 V	S
17.7 V	T
17.8 V	U
17.9 V	V
18.0 V	W

2. Function list of product types

Table 2

Product Type	Hysteresis Width (V_{UVHYS}, V_{OVHYS})	UV, OV Pin Output Form	UV, OV Pin Output Logic
L type	0%	Nch open-drain output	Active "L"
M type	5.0%	Nch open-drain output	Active "L"
N type	10.0%	Nch open-drain output	Active "L"

3. Packages

Table 3 Package Drawing Codes

Package Name	Dimension	Tape	Reel	Land
HTMSOP-8	FP008-A-P-SD	FP008-A-C-SD	FP008-A-R-SD	FP008-A-L-SD
HSNT-8(2030)	PP008-A-P-SD	PP008-A-C-SD	PP008-A-R-SD	PP008-A-L-SD

■ Pin Configurations

1. HTMSOP-8

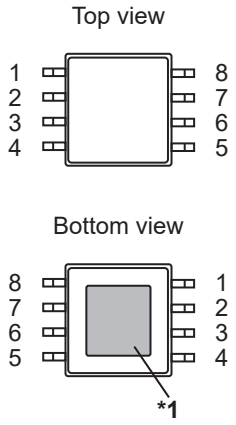


Figure 3

Table 4

Pin No.	Symbol	Description
1	NC*2	No connection
2	VDD	Voltage input pin
3	NC*2	No connection
4	SENSE	Detection voltage input pin
5	CD*3	Connection pin for release delay time adjustment capacitor
6	VSS	GND pin
7	UV	Undervoltage detection output pin
8	OV	Overvoltage detection output pin

***1.** Connect the heat sink of backside at shadowed area to the board, and set electric potential GND.
However, do not use it as the function of electrode.
***2.** The NC pin is electrically open.
The NC pin can be connected to the VDD pin or the VSS pin.
***3.** Connect a capacitor between the CD pin and the VSS pin. The release delay time can be adjusted according to the capacitance.

2. HSNT-8(2030)

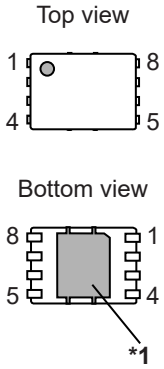


Figure 4

Table 5

Pin No.	Symbol	Description
1	NC*2	No connection
2	VDD	Voltage input pin
3	NC*2	No connection
4	SENSE	Detection voltage input pin
5	CD*3	Connection pin for release delay time adjustment capacitor
6	VSS	GND pin
7	UV	Undervoltage detection output pin
8	OV	Overvoltage detection output pin

***1.** Connect the heat sink of backside at shadowed area to the board, and set electric potential GND.
However, do not use it as the function of electrode.
***2.** The NC pin is electrically open.
The NC pin can be connected to the VDD pin or the VSS pin.
***3.** Connect a capacitor between the CD pin and the VSS pin. The release delay time can be adjusted according to the capacitance.

■ Absolute Maximum Ratings

Table 6

(Ta = –40°C to +125°C unless otherwise specified)

Item	Symbol	Absolute Maximum Rating	Unit
Power supply voltage	V_{DD}	V_{SS} – 0.3 to V_{SS} + 45.0	V
SENSE pin voltage	V_{SENSE}	V_{SS} – 30.0 to V_{SS} + 45.0	V
CD pin input voltage	V_{CD}	V_{SS} – 0.3 to V_{DD} + 0.3 ≤ V_{SS} + 7.0	V
Output voltage	V_{UV}	V_{SS} – 0.3 to V_{SS} + 45.0	V
	V_{OV}	V_{SS} – 0.3 to V_{SS} + 45.0	V
Output current	I_{UV}	25	mA
	I_{OV}	25	mA
Junction temperature	T_j	–40 to +150	°C
Operation ambient temperature	T_{opr}	–40 to +125	°C
Storage temperature	T_{stg}	–40 to +150	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Thermal Resistance Value

Table 7

Item	Symbol	Condition		Min.	Typ.	Max.	Unit
Junction-to-ambient thermal resistance*1	θ_{JA}	HTMSOP-8	Board A	–	159	–	°C/W
			Board B	–	113	–	°C/W
			Board C	–	39	–	°C/W
			Board D	–	40	–	°C/W
			Board E	–	30	–	°C/W
		HSNT-8(2030)	Board A	–	181	–	°C/W
			Board B	–	135	–	°C/W
			Board C	–	40	–	°C/W
			Board D	–	42	–	°C/W
			Board E	–	32	–	°C/W

***1.** Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "■ **Power Dissipation**" and "**Test Board**" for details.

■ Electrical Characteristics

Table 8

(Ta = –40°C to +125°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Undervoltage detection voltage*1	V_{UVDET}	V_{DD} = 13.5 V, 4.0 V ≤ $V_{UVDET(S)}$ ≤ 10.0 V	$V_{UVDET(S)}$ × 0.985	$V_{UVDET(S)}$	$V_{UVDET(S)}$ × 1.015	V	1
Overvoltage detection voltage*2	V_{OVDET}	V_{DD} = 13.5 V, 16.0 V ≤ $V_{OVDET(S)}$ ≤ 18.0 V	$V_{OVDET(S)}$ × 0.985	$V_{OVDET(S)}$	$V_{OVDET(S)}$ × 1.015	V	1
Undervoltage hysteresis width*3	V_{UVHYS}	L type (V_{UVHYS} = 0%)	–	V_{UVDET} × 0.00	–	V	1
		M type (V_{UVHYS} = 5.0%)	V_{UVDET} × 0.04	V_{UVDET} × 0.05	V_{UVDET} × 0.06	V	1
		N type (V_{UVHYS} = 10.0%)	V_{UVDET} × 0.09	V_{UVDET} × 0.10	V_{UVDET} × 0.11	V	1
Overvoltage hysteresis width*3	V_{OVHYS}	L type (V_{OVHYS} = 0%)	–	V_{OVDET} × 0.00	–	V	1
		M type (V_{OVHYS} = 5.0%)	V_{OVDET} × 0.04	V_{OVDET} × 0.05	V_{OVDET} × 0.06	V	1
		N type (V_{OVHYS} = 10.0%)	V_{OVDET} × 0.09	V_{OVDET} × 0.10	V_{OVDET} × 0.11	V	1
Current consumption	I_{SS1}	V_{DD} = 13.5 V, V_{SENSE} = 13.5 V	–	0.9	3.2	µA	4
Operation voltage	V_{DD}	–	3.0	–	36.0	V	1
Output current	I_{OUT}	UV pin Nch driver, V_{DD} = 3.0 V, V_{DS}*4 = 0.1 V, V_{SENSE} = $V_{UVDET(S)}$ – 1 V	0.60	–	–	mA	2
		OV pin Nch driver, V_{DD} = 3.0 V, V_{DS}*4 = 0.1 V, V_{SENSE} = $V_{OVDET(S)}$ + 1 V	0.60	–	–	mA	2
Leakage current	I_{LEAK}	UV pin Nch driver, V_{DD} = 36 V, V_{UV} = 36 V, V_{SENSE} = 13.5 V	–	–	2.0	µA	2
		OV pin Nch driver, V_{DD} = 36 V, V_{OV} = 36 V, V_{SENSE} = 13.5 V	–	–	2.0	µA	2
Detection response time*5	t_{RESET}	–	–	80	200	µs	3
Release delay time*6	t_{DELAY}	C_D = 3.3 nF	8.5	10.0	11.5	ms	3
SENSE pin resistance	R_{SENSE}	–	6.8	–	200	MΩ	4
CD pin discharge ON resistance	R_{CDD}	V_{DD} = 3.0 V, V_{CD} = 0.7 V	0.15	–	0.90	kΩ	–

***1.** V_{UVDET}: Actual undervoltage detection voltage value, $V_{UVDET(S)}$: Set undervoltage detection voltage value

***2.** V_{OVDET}: Actual overvoltage detection voltage value, $V_{OVDET(S)}$: Set overvoltage detection voltage value

***3.** The undervoltage release voltage (V_{UVREL}) and the overvoltage release voltage (V_{OVREL}) are as follows.
L type (hysteresis width "Unavailable"): V_{UVREL} = V_{UVDET}, V_{OVREL} = V_{OVDET}
M / N type (hysteresis width "Available"): V_{UVREL} = V_{UVDET} + V_{UVHYS}, V_{OVREL} = V_{OVDET} – V_{OVHYS}

***4.** V_{DS}: Drain-to-source voltage of the output transistor

***5.** The time period from when the pulse voltage of $V_{UVDET(S)}$ + 1.0 V → $V_{UVDET(S)}$ – 1.0 V or $V_{OVDET(S)}$ – 1.0 V → $V_{OVDET(S)}$ + 1.0 V is applied to the SENSE pin after V_{SENSE} reaches the release voltage once, until V_{UV} or V_{OV} reaches 50% of V_{DD}.

***6.** $V_{UVREL(S)}$: Set undervoltage release voltage value, $V_{OVREL(S)}$: Set overvoltage release voltage value
The time period from when the pulse voltage of $V_{UVREL(S)}$ – 1.0 V → $V_{UVREL(S)}$ + 1.0 V or $V_{OVREL(S)}$ + 1.0 V → $V_{OVREL(S)}$ – 1.0 V is applied to the SENSE pin to when V_{UV} or V_{OV} reaches 50% of V_{DD}.

■ Test Circuits

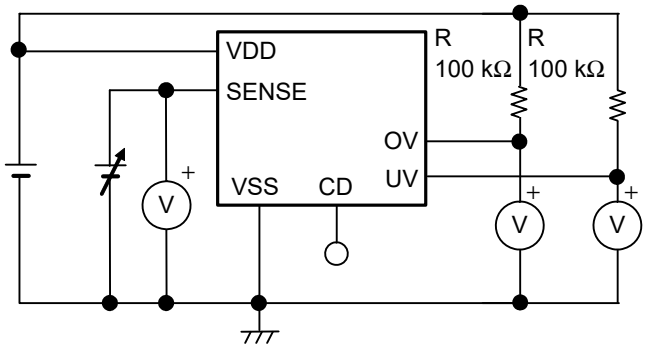


Figure 5 Test Circuit 1

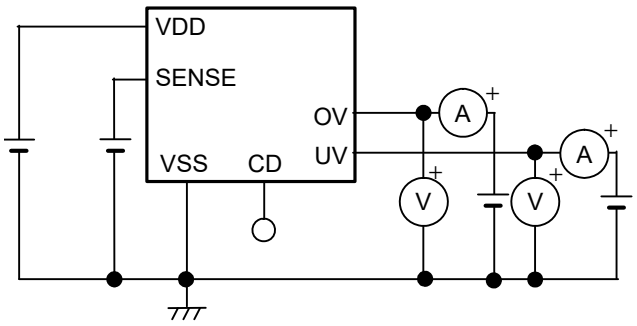


Figure 6 Test Circuit 2

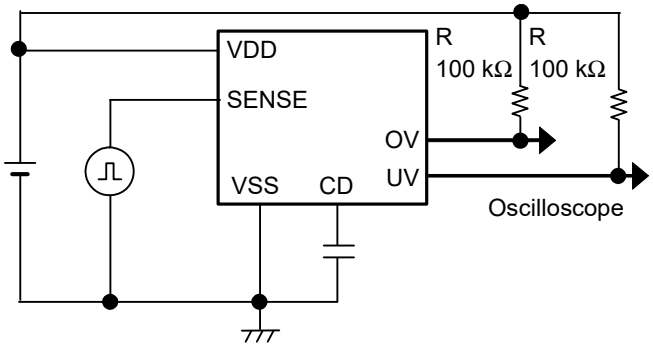


Figure 7 Test Circuit 3

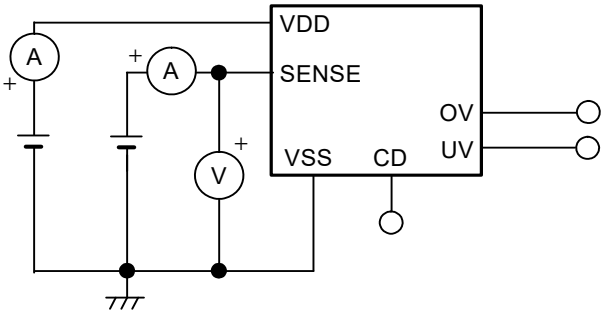
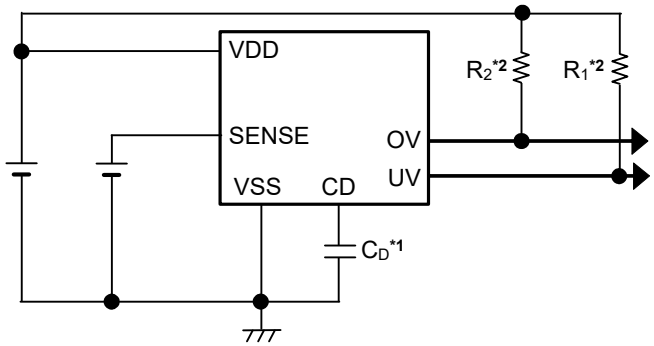


Figure 8 Test Circuit 4

■ Standard Circuit



***1.** C_D is a release delay time adjustment capacitor. The C_D should be connected directly to the CD pin and the VSS pin.

***2.** R_1, R_2 are the external pull-up resistors for the reset output pin.

Figure 9

Caution The above connection diagram and constants will not guarantee successful operation. Perform thorough evaluation including the temperature characteristics with an actual application to set the constants.

■ Condition of Application

Release delay time adjustment capacitor (C_D): A ceramic capacitor with capacitance of 1.0 nF or more is recommended.

■ Selection of Release Delay Time Adjustment Capacitor (C_D)

In this IC, the release delay time adjustment capacitor (C_D) is necessary between the CD pin and the VSS pin to adjust the release delay time (t_{DELAY}) of the detector. Refer to "**1. 4 Delay circuit**" in "**■ Operation**" for details.

Caution Perform thorough evaluation including the temperature characteristics with an actual application to select C_D.

■ Explanation of Terms

1. Detection voltage (V_{UVDET}, V_{OVDET})

The detection voltage is a SENSE pin voltage at which the output voltage in **Figure 14** turns to "L". The detection voltage varies slightly among products of the same specification. The variation of detection voltage between the specified minimum and the maximum is called the detection voltage range (Refer to "**Figure 10 Overvoltage Detection Voltage**", "**Figure 12 Undervoltage Detection Voltage**").

Table 9

Detection Operation	Detection Voltage	Output Voltage	Detection Voltage Range
Undervoltage detection	V_{UVDET}	V_{UV} = "H" → "L"	V_{UVDET} min. to V_{UVDET} max.
Overvoltage detection	V_{OVDET}	V_{OV} = "H" → "L"	V_{OVDET} min. to V_{OVDET} max.

Example: In V_{UVDET} = 4.0 V product, the detection voltage is at any point in the range of 3.940 V ≤ V_{UVDET} ≤ 4.060 V.
This means that some V_{UVDET} = 4.0 V product has V_{UVDET} = 3.940 V and some has V_{UVDET} = 4.060 V.

2. Release voltage (V_{UVREL}, V_{OVREL})

The release voltage is a SENSE pin voltage at which the output voltage in **Figure 14** turns to "H". The release voltage varies slightly among products of the same specification. The variation of release voltage between the specified minimum and the maximum is called the release voltage range (Refer to "**Figure 11 Overvoltage Release Voltage**", "**Figure 13 Undervoltage Release Voltage**").
The release voltage becomes the value differs from the detection voltage within the range shown below.

- M type: 4% to 6% (5% typ.)
- N type: 9% to 11% (10% typ.)

Table 10

Detection Operation	Release Voltage	Output Voltage	Release Voltage Range
Undervoltage detection	V_{UVREL}	V_{UV} = "L" → "H"	V_{UVREL} min. to V_{UVREL} max.
Overvoltage detection	V_{OVREL}	V_{OV} = "L" → "H"	V_{OVREL} min. to V_{OVREL} max.

Example: For N type, V_{UVDET} = 4.0 V product, the release voltage is at any point in the range of 4.294 V ≤ V_{UVREL} ≤ 4.507 V despite V_{UVREL} = 4.400 V typ.
This means that some N type, V_{UVDET} = 4.0 V product has V_{UVREL} = 4.294 V and some has V_{UVREL} = 4.507 V.

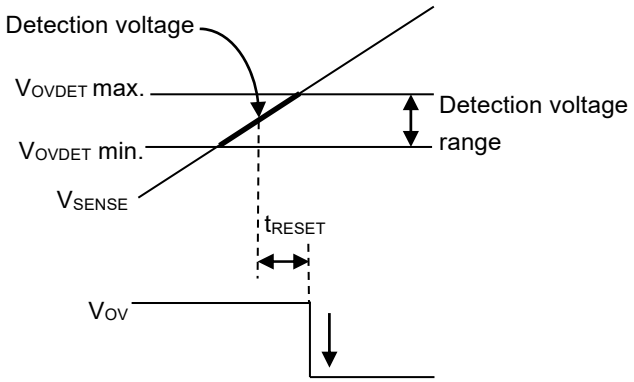


Figure 10 Overvoltage Detection Voltage

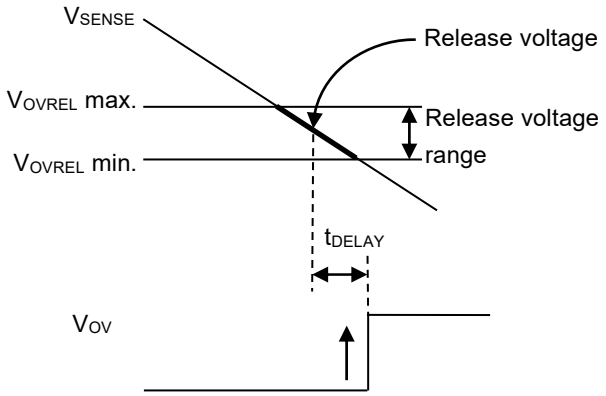


Figure 11 Overvoltage Release Voltage

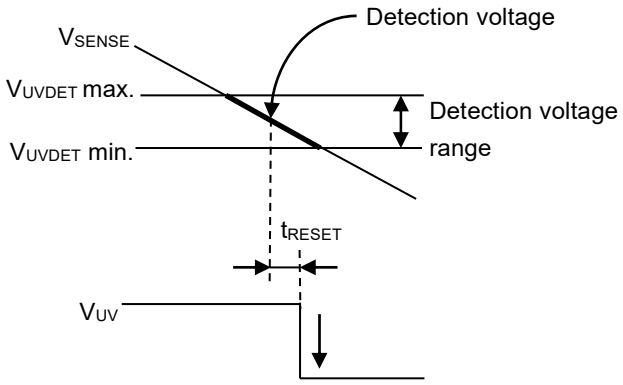


Figure 12 Undervoltage Detection Voltage

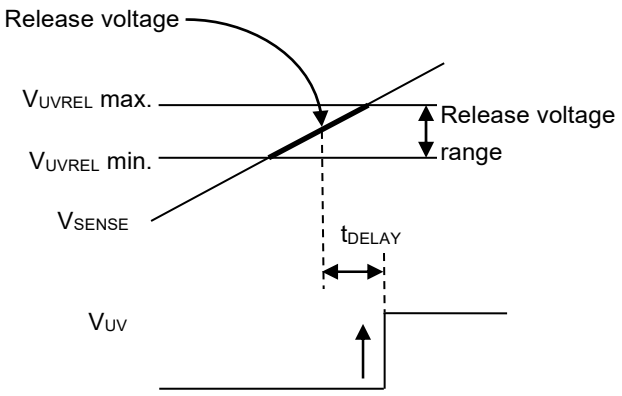


Figure 13 Undervoltage Release Voltage

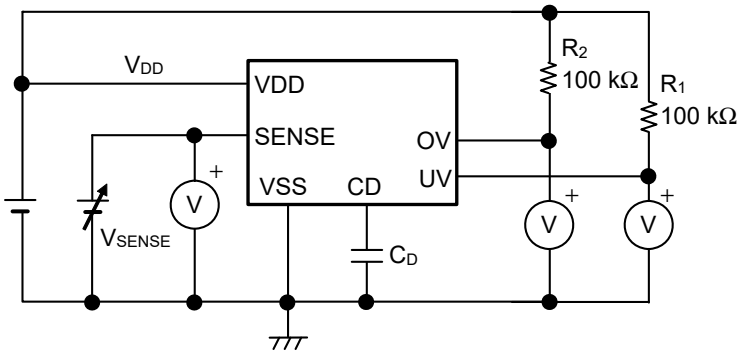


Figure 14 Test Circuit of Detection Voltage and Release Voltage

3. Hysteresis width (V_{UVHYS}, V_{OVHYS})

The hysteresis width is the voltage difference between the detection voltage and the release voltage. Setting the hysteresis width between the detection voltage and the release voltage, prevents malfunction caused by noise on the input voltage.

- Undervoltage hysteresis width (V_{UVHYS}): $V_{UVREL} - V_{UVDET}$
- Overvoltage hysteresis width (V_{OVHYS}): $V_{OVDET} - V_{OVREL}$

4. Feed-through current

The feed-through current is a current that flows instantaneously to the VDD pin at the time of detection and release of a voltage detector.

■ Operation

1. Basic operation

Figure 15 and **Figure 17** show that the UV and OV pins being pulled up by resistors (R_1, R_2) is an example of basic detector block operation.

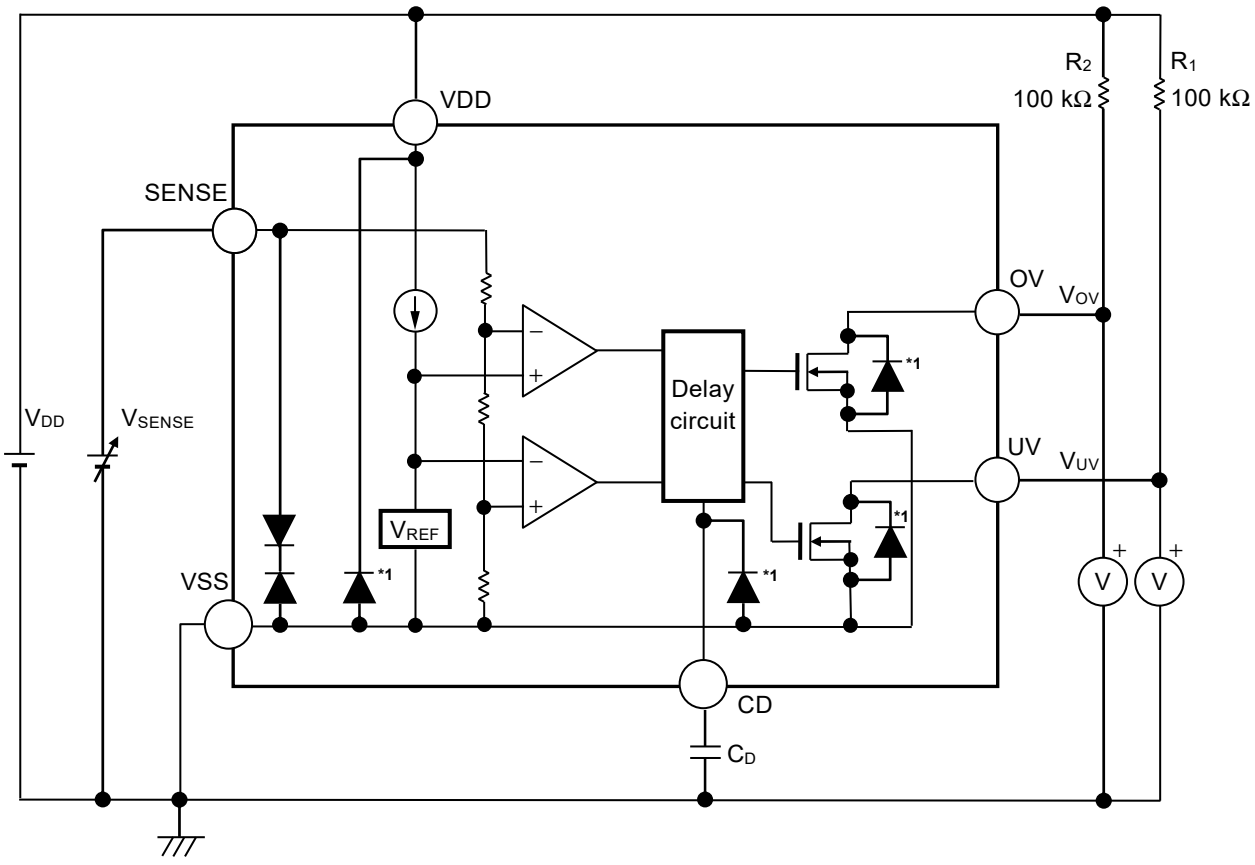
1. 1 S-191E Series L type

(1) Undervoltage detection status to release status (undervoltage release status)
When the SENSE pin voltage (V_{SENSE}) exceeds the undervoltage release voltage (V_{UVREL} = V_{UVDET}), the UV pin voltage output becomes "H" after release delay time (t_{DELAY}). At this time, the OV pin output stays at "H".

(2) Release status to overvoltage detection status
V_{SENSE} rises, and when it exceeds the overvoltage detection voltage (V_{OVDET}), the OV pin output becomes "L" after detection response time (t_{RESET}). At this time, the UV pin stays at "H".

(3) Overvoltage detection status to release status (overvoltage release status)
V_{SENSE} drops, and when it goes below the overvoltage release voltage (V_{OVREL} = V_{OVDET}), the OV pin output changes to "H" after t_{DELAY}. At this time, the UV pin output stays at "H".

(4) Release status to undervoltage detection status
V_{SENSE} drops, and when it goes below the undervoltage detection voltage (V_{UVDET}), the UV pin output becomes "L" after t_{RESET} and changes to undervoltage detection status. At this time, the OV pin output stays at "H".



***1.** Parasitic diode

Figure 15 Operation of S-191E Series L type

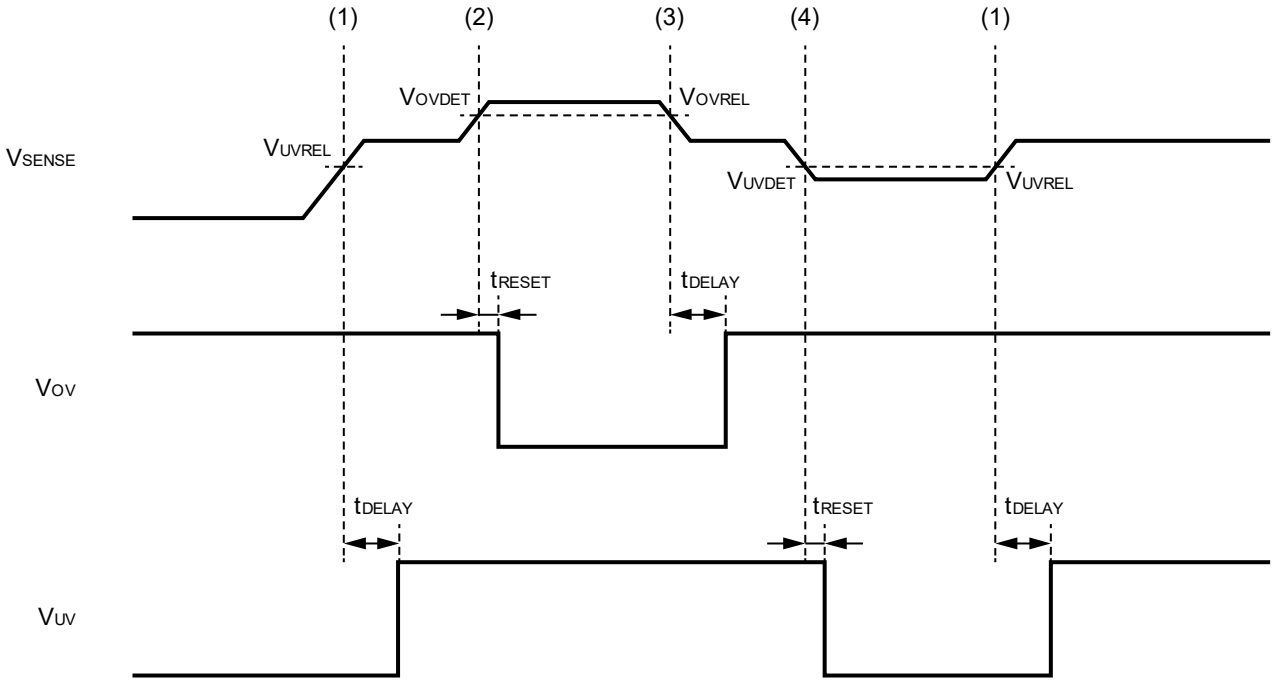


Figure 16 Timing Chart of S-191E Series L Type

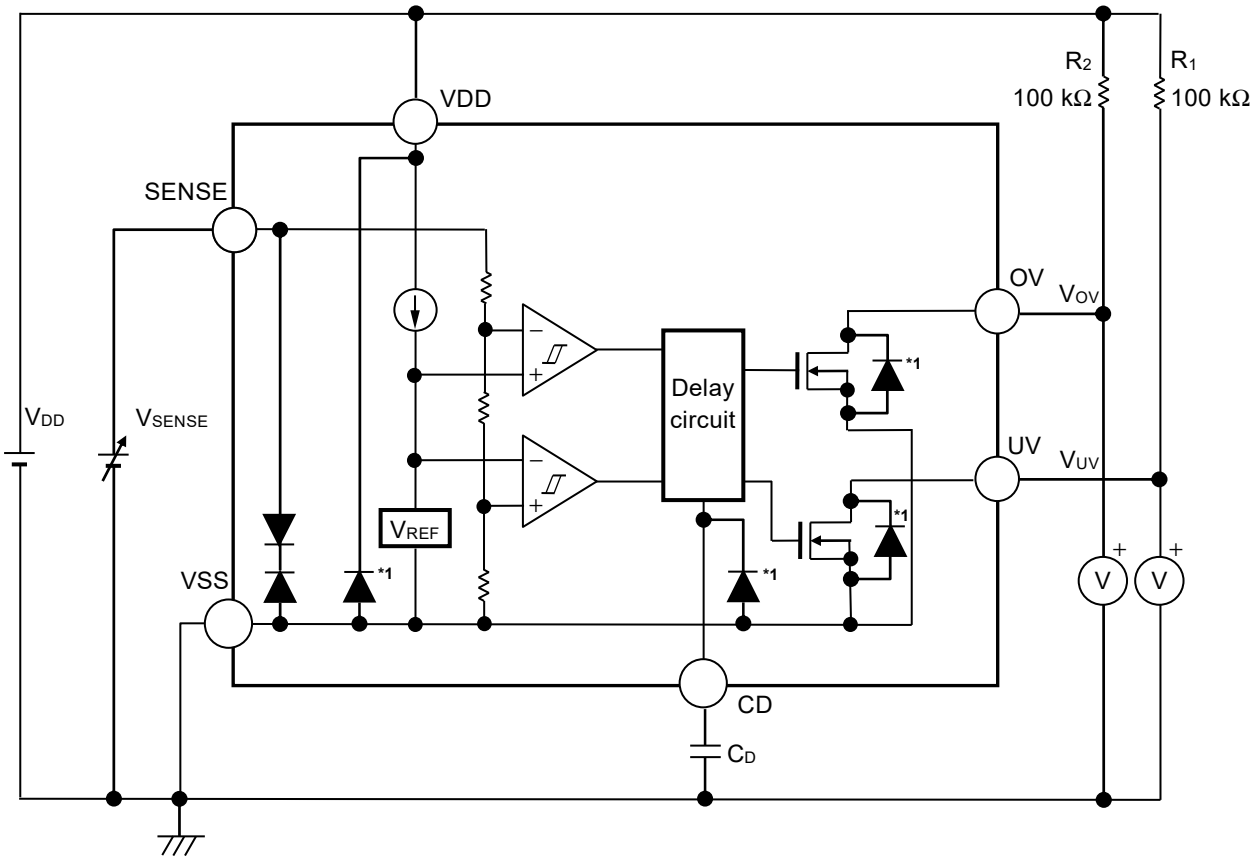
1. 2 S-191E Series M / N type

(1) Undervoltage detection status to release status (undervoltage release status)
When the SENSE pin voltage (V_{SENSE}) exceeds the undervoltage release voltage (V_{UVREL} = V_{UVDET} + V_{UVHYS}), the UV pin voltage output becomes "H" after release delay time (t_{DELAY}). At this time, the OV pin output stays at "H".

(2) Release status to overvoltage detection status
V_{SENSE} rises, and when it exceeds the overvoltage detection voltage (V_{OVDET}), the OV pin output becomes "L" after detection response time (t_{RESET}). At this time, the UV pin stays at "H".

(3) Overvoltage detection status to release status (overvoltage release status)
V_{SENSE} drops, and when it goes below the overvoltage release voltage (V_{OVREL} = V_{OVDET} – V_{OVHYS}), the OV pin output changes to "H" after t_{DELAY}. At this time, the UV pin output stays at "H".

(4) Release status to undervoltage detection status
V_{SENSE} drops, and when it goes below the undervoltage detection voltage (V_{UVDET}), the UV pin output becomes "L" after t_{RESET} and changes to undervoltage detection status. At this time, the OV pin output stays at "H".



***1.** Parasitic diode

Figure 17 Operation of S-191E Series M / N type

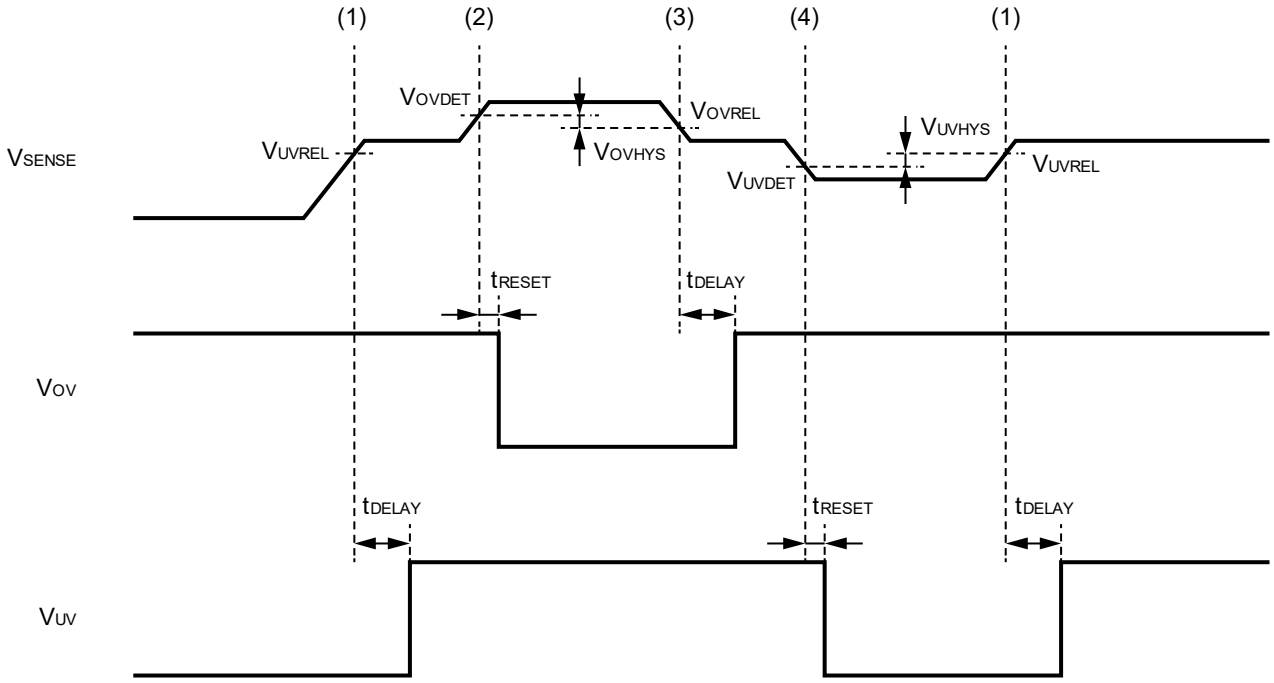


Figure 18 Timing Chart of S-191E Series M / N Type

1. 3 SENSE pin

The SENSE pin is the input pin for the detection voltage. The power supply VDD pin and SENSE pin, for voltage detection, are divided. Therefore, as long as a voltage is supplied to the VDD pin, the reset signal will be held even if the input voltage to the SENSE pin drops below the minimum operation voltage. Also, the SENSE pin of this IC has a built-in reverse connection protection circuit. Even when the SENSE pin voltage is less than the VSS pin voltage, the voltage flowing from the VSS pin to the SENSE pin is reduced to 0.05 mA typ.

1. 3. 1 Error when detection voltage is set externally

The undervoltage detection voltage and the overvoltage detection voltage can be set externally by connecting a node that was resistance-divided by the resistor (R_A) and the resistor (R_B) to the SENSE pin as shown in **Figure 19**.

For conventional products without the SENSE pin, external resistor cannot be too large since the resistance-divided node must be connected to the VDD pin. This is because a feed-through current will flow through the VDD pin when it goes from detection to release, and if external resistor is large, problems such as oscillation or larger error in the hysteresis width may occur.

In this IC, R_A and R_B in **Figure 19** are easily made larger since the resistance-divided node can be connected to the SENSE pin through which no feed-through current flows. However, be careful of error in the current flowing through the internal resistance (R_{SENSE}) that will occur.

Although R_{SENSE}*1 in this IC is large to make the error small, R_A and R_B should be selected such that the error is within the allowable limits.

***1.** 6.8 MΩ min.

1. 3. 2 Selection of R_A and R_B

In **Figure 19**, the relation between the external setting undervoltage detection voltage (V_{DUX}) or the overvoltage detection voltage (V_{DOX}) and the actual detection voltage (V_{UVDET}, V_{OVDET}) is ideally calculated by the equation below.

$$V_{DUX} = V_{UVDET} \times \left(1 + \frac{R_A}{R_B}\right) \cdots\cdots(1)$$

$$V_{DOX} = V_{OVDET} \times \left(1 + \frac{R_A}{R_B}\right) \cdots\cdots(1)$$

However, in reality there is an error in the current flowing through R_{SENSE}.
When considering this error, the relation between V_{DUX}, V_{DOX} and V_{OVDET} is calculated as follows.

$$\begin{aligned} V_{DUX} &= V_{UVDET} \times \left(1 + \frac{R_A}{R_B \parallel R_{SENSE}}\right) \\ &= V_{UVDET} \times \left(1 + \frac{R_A}{\dfrac{R_B \times R_{SENSE}}{R_B + R_{SENSE}}}\right) \\ &= V_{UVDET} \times \left(1 + \frac{R_A}{R_B}\right) + \frac{R_A}{R_{SENSE}} \times V_{UVET} \cdots\cdots(2) \end{aligned}$$

$$V_{DOX} = V_{OVDET} \times \left(1 + \frac{R_A}{R_B}\right) + \frac{R_A}{R_{SENSE}} \times V_{OVET} \cdots\cdots(2)$$

By using equations (1) and (2), the error is calculated as $V_{UVDET} \times \frac{R_A}{R_{SENSE}}$, $V_{OVDET} \times \frac{R_A}{R_{SENSE}}$.
The error rate is calculated as follows by dividing the error by the right-hand side of equation (1).

$$\frac{R_A \times R_B}{R_{SENSE} \times (R_A + R_B)} \times 100\ [\%] = \frac{R_A \parallel R_B}{R_{SENSE}} \times 100\ [\%] \cdots(3)$$

As seen in equation (3), the smaller the resistance values of R_A and R_B compared to R_{SENSE}, the smaller the error rate becomes.

Also, the relation between the external setting undervoltage hysteresis width (V_{HUX}) or the overvoltage hysteresis width (V_{HOX}) and the hysteresis width (V_{UVHYS}, V_{OVHYS}) is calculated by equation below. Error due to R_{SENSE} also occurs to the relation in a similar way to the detection voltage.

$$V_{HUX} = V_{UVHYS} \times \left(1 + \frac{R_A}{R_B}\right) \cdots\cdots(4)$$

$$V_{HOX} = V_{OVHYS} \times \left(1 + \frac{R_A}{R_B}\right) \cdots\cdots(4)$$

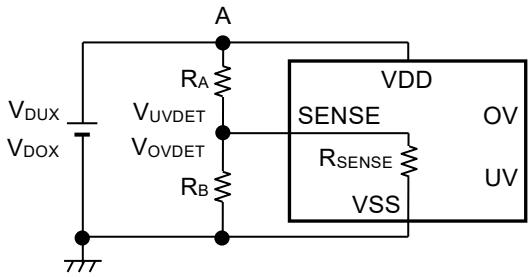


Figure 19 Detection Voltage External Setting Circuit

Caution If R_A and R_B are large, the SENSE pin input impedance becomes higher and may cause a malfunction due to noise. In this case, connect a capacitor between the SENSE pin and the VSS pin.

1. 4 Delay circuit

The delay circuit comes with a function for adjusting the release delay time (t_{DELAY}) from when the SENSE pin voltage (V_{SENSE}) enters the state in **Table 11** and until the output pin inverts.

Table 11

Release operation	Status	Output Pin
Undervoltage release	Undervoltage release voltage (V_{UVREL} = V_{UVDET} + V_{UVHYS}) or more	UV pin
Overvoltage release	Overvoltage release voltage (V_{OVREL} = V_{OVDET} – V_{OVHYS}) or lower	OV pin

t_{DELAY} is determined by the delay coefficient, the release delay time adjustment capacitor (C_D) and the release delay time when the CD pin is open (t_{DELAY0}). They are calculated by the equations below.

t_{DELAY} [ms] = Delay coefficient × C_D [nF] + t_{DELAY0} [ms]

Table 12

Operation Temperature	Delay Coefficient		
	Min.	Typ.	Max.
Ta = +125°C	2.65	3.03	3.41
Ta = +105°C	2.71	3.05	3.35
Ta = +25°C	2.92	3.06	3.14
Ta = –40°C	2.65	3.09	3.41

Table 13

Operation Temperature	Release Delay Time when CD Pin is Open (t_{DELAY0})		
	Min.	Typ.	Max.
Ta = +125°C	0.05	0.09	0.17
Ta = +105°C	0.05	0.10	0.17
Ta = +25°C	0.06	0.11	0.19
Ta = –40°C	0.06	0.13	0.25

Caution 1. Mounted board layout should be made in such a way that no current flows into or flows from the CD pin since the impedance of the CD pin is high, otherwise correct delay time cannot be provided.

2. There is no limit for the capacitance of C_D as long as the leakage current of the capacitor can be ignored against the built-in constant current value (approximately 160 nA). The leakage current may cause error in delay time. When the leakage current is larger than the built-in constant current, no detect or release takes place.

3. The above equations will not guarantee successful operation. Determine the capacitance of C_D through thorough evaluation including temperature characteristics in the actual usage conditions.

■ Usage Precautions

1. Power on sequence

Turn on the power in one of the following two procedures.

(1) Order of VDD pin and SENSE pin (Refer to **Figure 20**)
(2) VDD pin and SENSE pin at the same time

When $V_{OVDET} \geq V_{SENSE} \geq V_{UVREL}$ applies, both the overvoltage output voltage (V_{OV}) and the undervoltage output voltage (V_{UV}) become "H", and the detector enters release status.

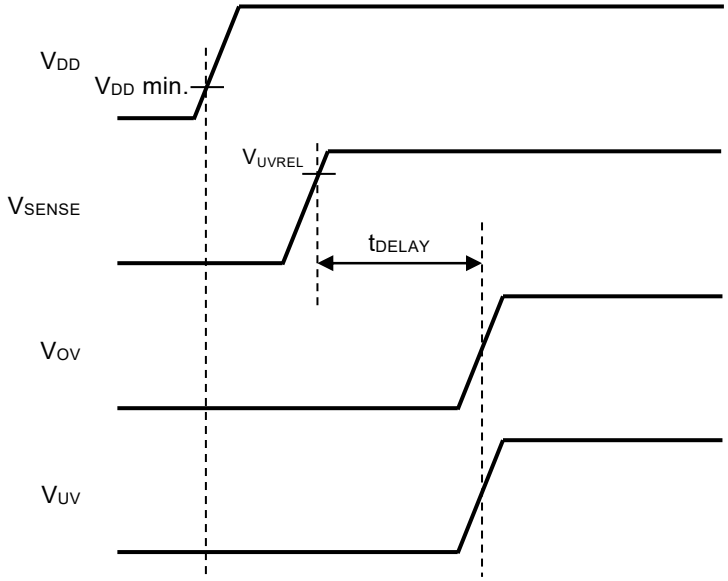


Figure 20

Caution When the SENSE pin is turned on before the VDD pin, a release may mistakenly occur even if V_{SENSE} is less than V_{UVREL}.

2. SENSE pin voltage glitch (Typical data)

2. 1 Undervoltage detection operation

Figure 21 shows the relation between pulse width and pulse voltage difference (V_{OD}) where the undervoltage release status can be maintained when a pulse equal to or lower than the undervoltage detection voltage (V_{UVDET}) is input to the SENSE pin during undervoltage release status.

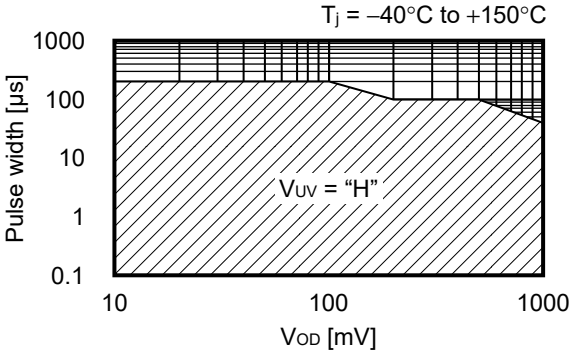
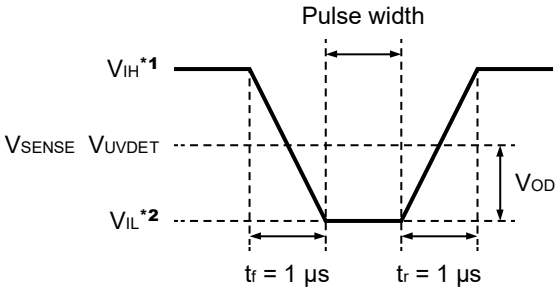


Figure 21



***1.** V_{IH} = 13.5 V
***2.** $V_{IL} = V_{UVDET} - V_{OD}$

Figure 22 SENSE Pin Input Voltage Waveform

Caution Figure 21 shows the pulse condition which can maintain the undervoltage release status. If the pulse whose pulse width and V_{OD} are larger than this condition is input to the SENSE pin, the UV pin may change to an undervoltage detection status.

2. 2 Undervoltage release operation

Figure 23 shows the relation between pulse width and pulse voltage difference (V_{OD}) where the undervoltage detection status can be maintained when a pulse equal to or higher than the undervoltage release voltage (V_{UVREL}) is input to the SENSE pin during undervoltage detection status.

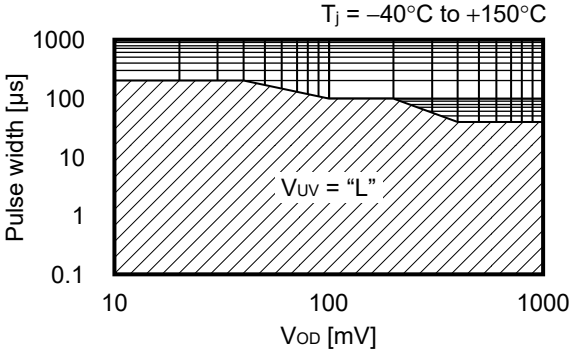
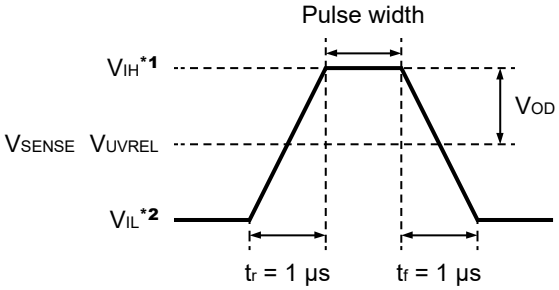


Figure 23



***1.** $V_{IH} = V_{UVREL} + V_{OD}$
***2.** $V_{IL} = V_{UVDET} - 1.0$ V

Figure 24 SENSE Pin Input Voltage Waveform

Caution Figure 23 shows the pulse condition which can maintain the undervoltage detection status. If the pulse whose pulse width and V_{OD} are larger than this condition is input to the SENSE pin, the UV pin may change to an undervoltage release status.

2. 3 Overvoltage detection operation

Figure 25 shows the relation between pulse width and pulse voltage difference (V_{OD}) where the overvoltage release status can be maintained when a pulse equal to or higher than the overvoltage detection voltage (V_{OVDET}) is input to the SENSE pin during overvoltage release status.

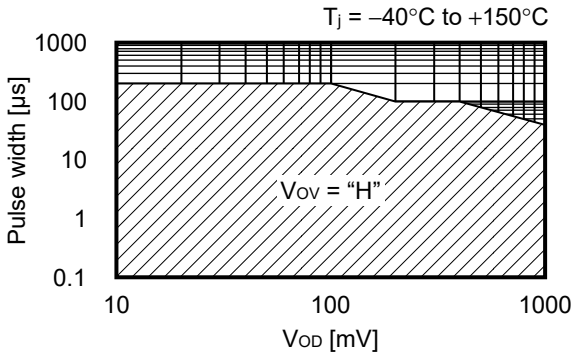
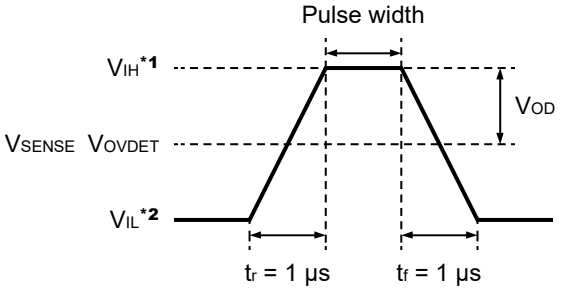


Figure 25



***1.** $V_{IH} = V_{OVDET} + V_{OD}$
***2.** V_{IL} = 13.5 V

Figure 26 SENSE Pin Input Voltage Waveform

Caution Figure 25 shows the pulse condition which can maintain the overvoltage release status. If the pulse whose pulse width and V_{OD} are larger than this condition is input to the SENSE pin, the OV pin may change to an overvoltage detection status.

2. 4 Overvoltage release operation

Figure 27 shows the relation between pulse width and pulse voltage difference (V_{OD}) where the overvoltage detection status can be maintained when a pulse equal to or lower than the overvoltage release voltage (V_{OVREL}) is input to the SENSE pin during overvoltage detection status.

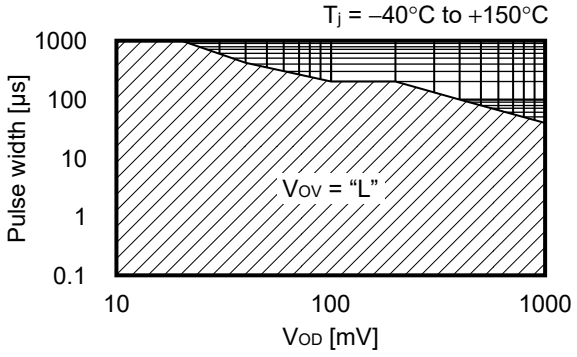
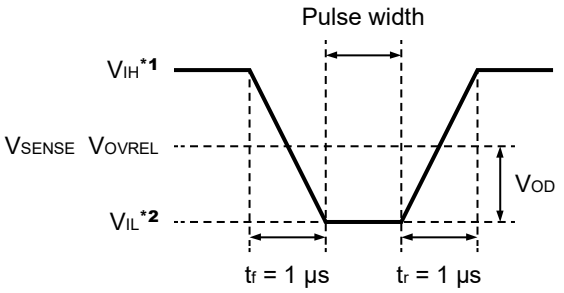


Figure 27



***1.** $V_{IH} = V_{OVDET} + 1.0$ V
***2.** $V_{IL} = V_{OVREL} - V_{OD}$

Figure 28 SENSE Pin Input Voltage Waveform

Caution Figure 27 shows the pulse condition which can maintain the overvoltage detection status. If the pulse whose pulse width and V_{OD} are larger than this condition is input to the SENSE pin, the OV pin may change to an overvoltage release status.

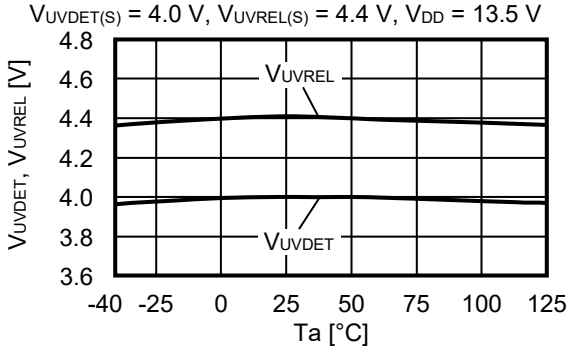
■ Precautions

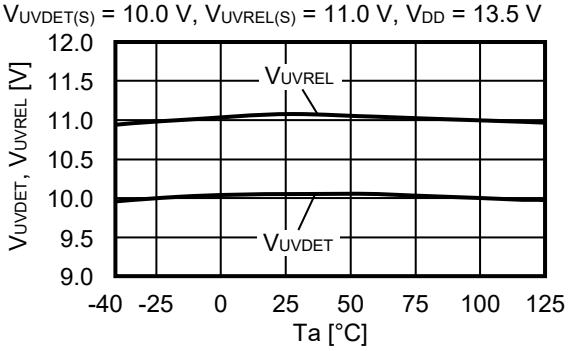
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- Because the SENSE pin has a high impedance, malfunctions may occur due to noise.
  Be careful of wiring adjoining SENSE pin wiring in actual applications.
- When designing for mass production using an application circuit described herein, the product deviation and temperature characteristics should be taken into consideration. ABLIC Inc. shall not bear any responsibility for patent infringements related to products using the circuits described herein.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

■ Characteristics (Typical Data)

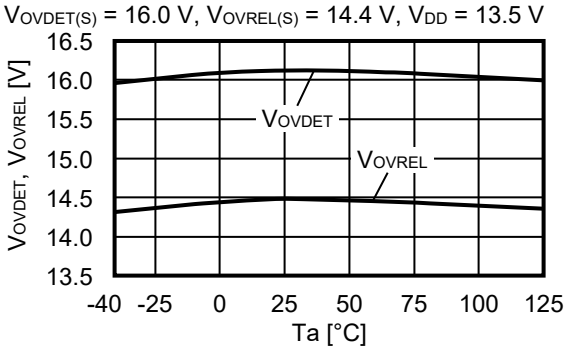
1. Detection voltage (V_{UVDET}, V_{OVDET}), Release voltage (V_{UVREL}, V_{OVREL}) vs. Temperature (Ta)

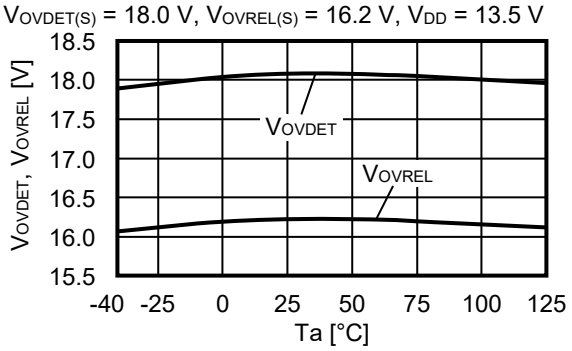
1. 1 Undervoltage detection





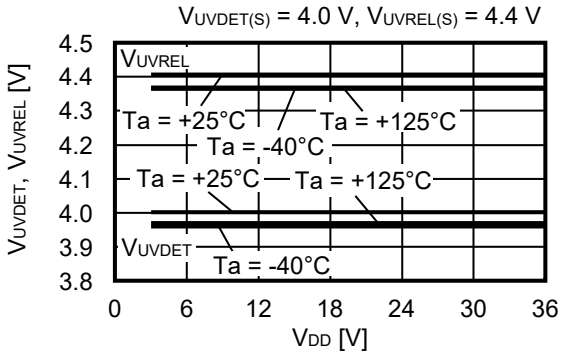
1. 2 Overvoltage detection

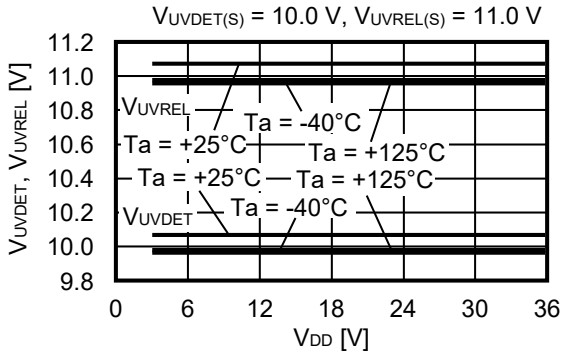




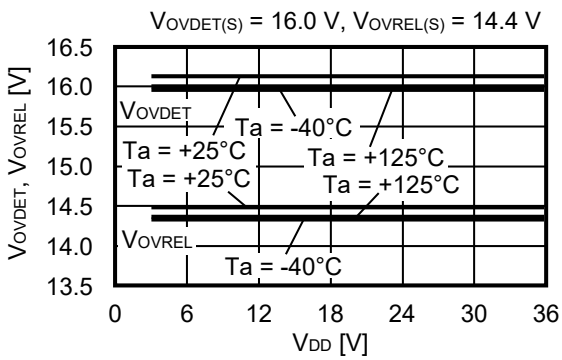
2. Detection voltage (V_{UVDET}, V_{OVDET}), Release voltage (V_{UVREL}, V_{OVREL}) vs. Power supply voltage (V_{DD})

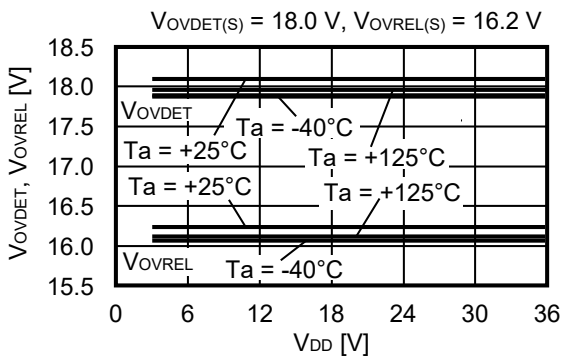
2. 1 Undervoltage detection





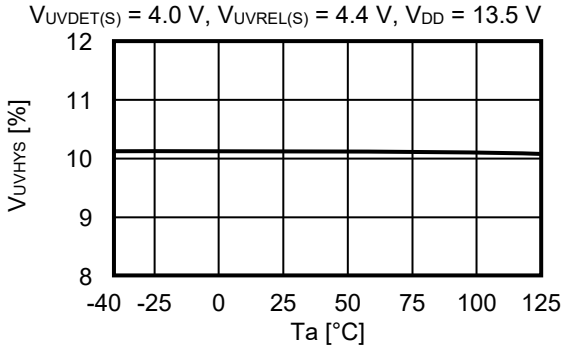
2. 2 Overvoltage detection

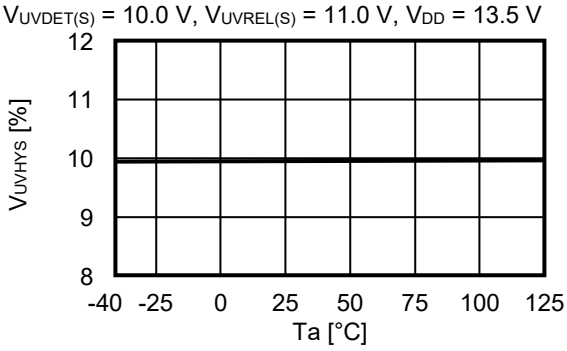




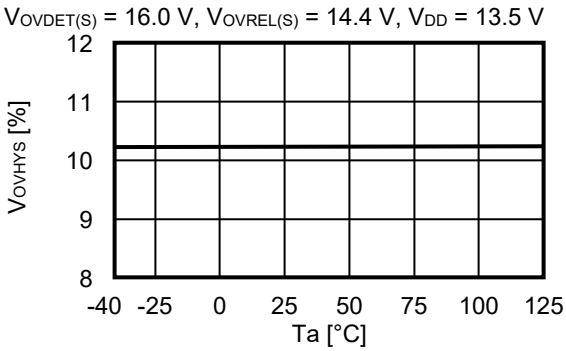
3. Hysteresis width (V_{UVHYS}, V_{OVHYS}) vs. Temperature (Ta)

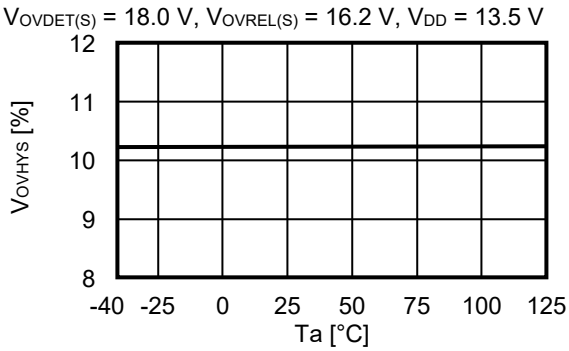
3. 1 Undervoltage detection





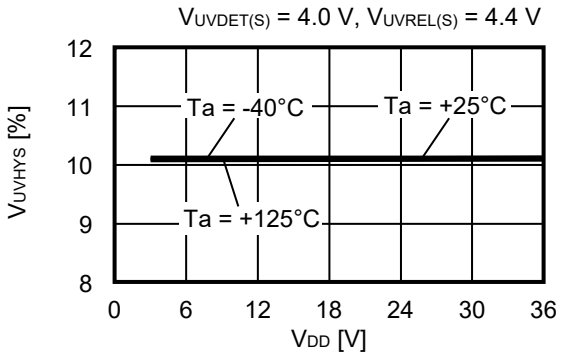
3. 2 Overvoltage detection

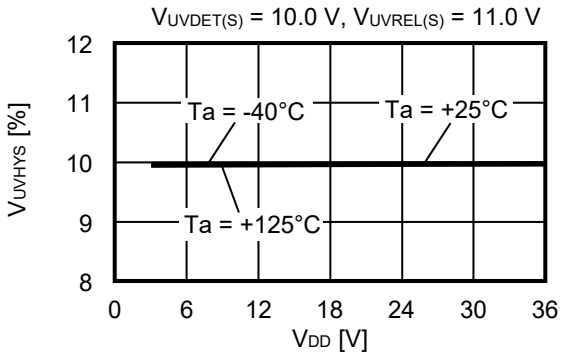




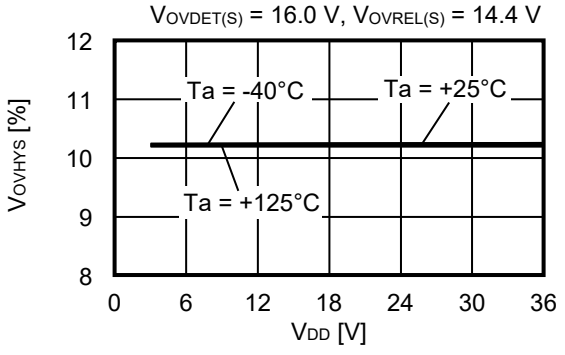
4. Hysteresis width (V_{UVHYS}, V_{OVHYS}) vs. Power supply voltage (V_{DD})

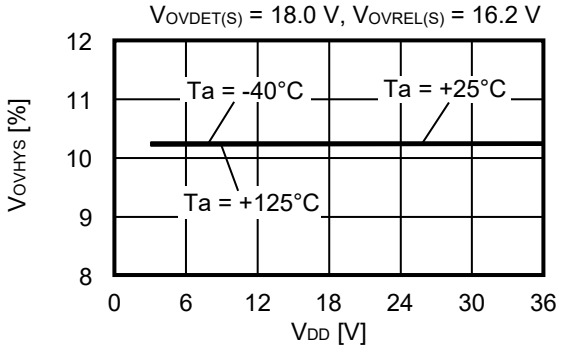
4. 1 Undervoltage detection





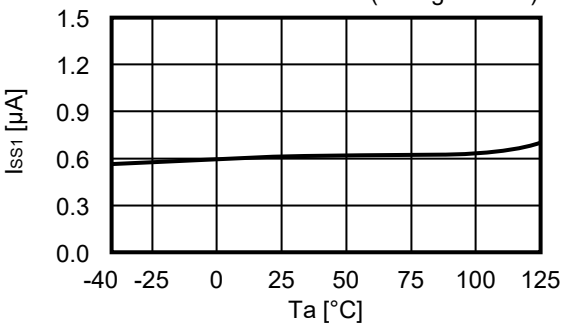
4. 2 Overvoltage detection



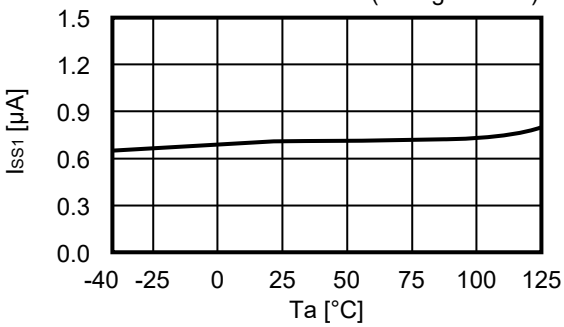


5. Current consumption (I_{SS1}) vs. Temperature (Ta)

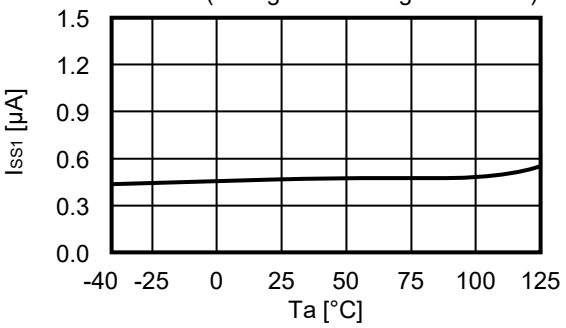
$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{DD} = 13.5 V, V_{SENSE} = 13.5 V
(during release)



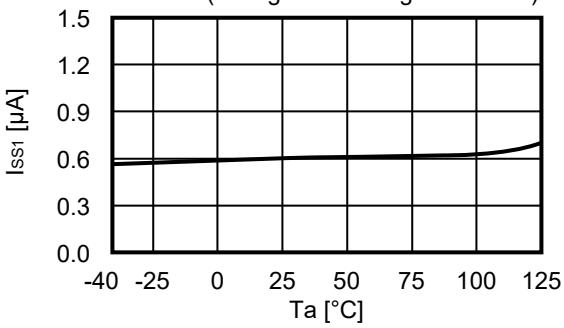
$V_{UVDET(S)}$ = 10.0 V, $V_{OVDET(S)}$ = 16.0 V,
V_{DD} = 13.5 V, V_{SENSE} = 13.5 V
(during release)



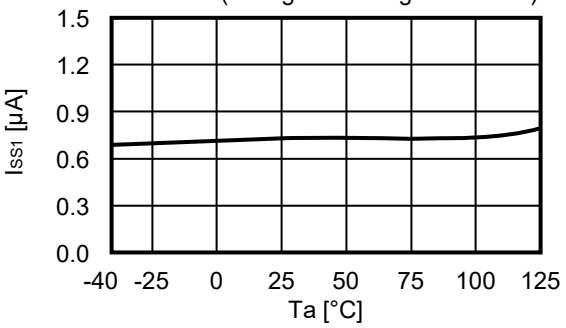
$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{DD} = 13.5 V, V_{SENSE} = 3.0 V
(during undervoltage detection)



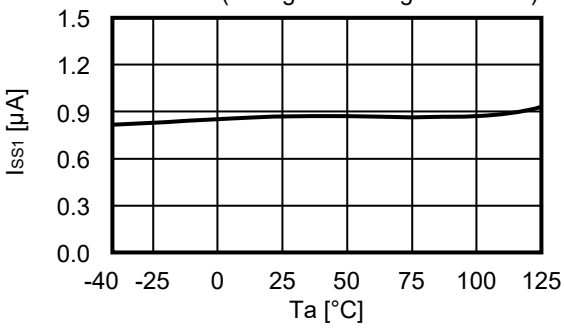
$V_{UVDET(S)}$ = 10.0 V, $V_{OVDET(S)}$ = 16.0 V,
V_{DD} = 13.5 V, V_{SENSE} = 9.0 V
(during undervoltage detection)



$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{DD} = 13.5 V, V_{SENSE} = 19.0 V
(during overvoltage detection)

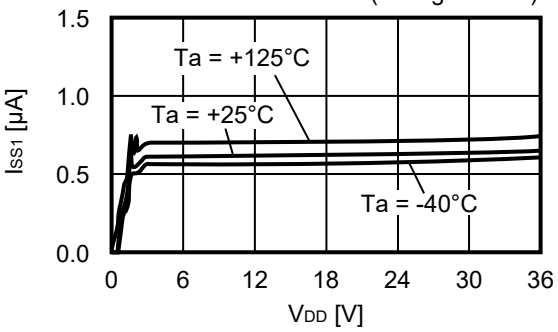


$V_{UVDET(S)}$ = 10.0 V, $V_{OVDET(S)}$ = 16.0 V,
V_{DD} = 13.5 V, V_{SENSE} = 17.0 V
(during overvoltage detection)

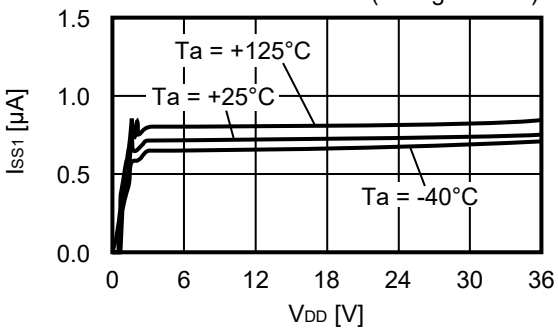


6. Current consumption (I_{SS1}) vs. Power supply voltage (V_{DD}) (No load)

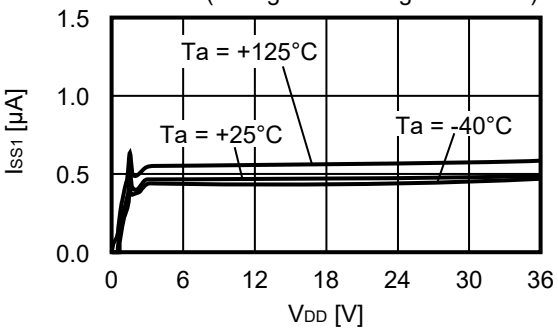
$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{DD} = 0 V → 36.0 V, V_{SENSE} = 13.5 V
(during release)



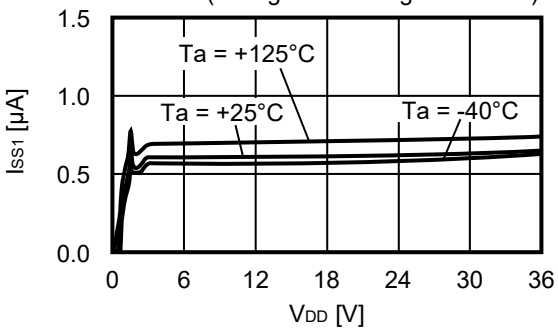
$V_{UVDET(S)}$ = 10.0 V, $V_{OVDET(S)}$ = 16.0 V,
V_{DD} = 0 V → 36.0 V, V_{SENSE} = 13.5 V
(during release)



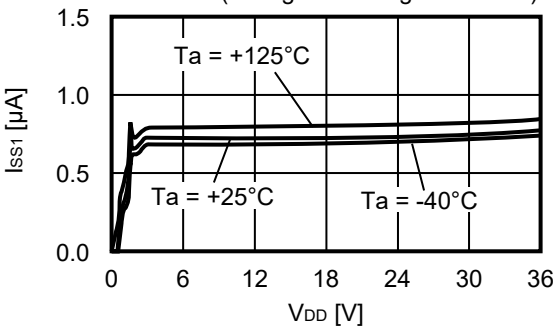
$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{DD} = 0 V → 36.0 V, V_{SENSE} = 3.0 V
(during undervoltage detection)



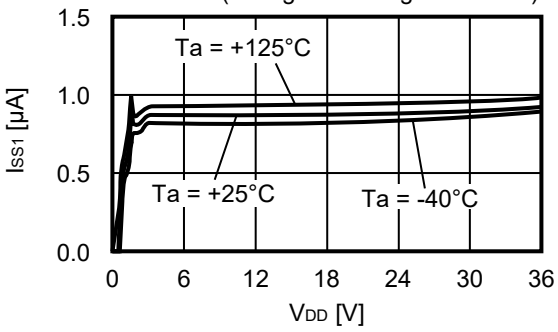
$V_{UVDET(S)}$ = 10.0 V, $V_{OVDET(S)}$ = 16.0 V,
V_{DD} = 0 V → 36.0 V, V_{SENSE} = 9.0 V
(during undervoltage detection)



$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{DD} = 0 V → 36.0 V, V_{SENSE} = 19.0 V
(during overvoltage detection)



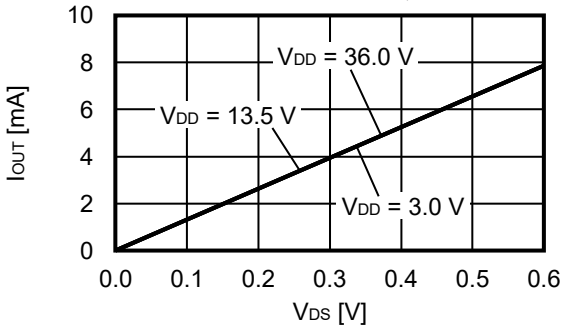
$V_{UVDET(S)}$ = 10.0 V, $V_{OVDET(S)}$ = 16.0 V,
V_{DD} = 0 V → 36.0 V, V_{SENSE} = 17.0 V
(during overvoltage detection)



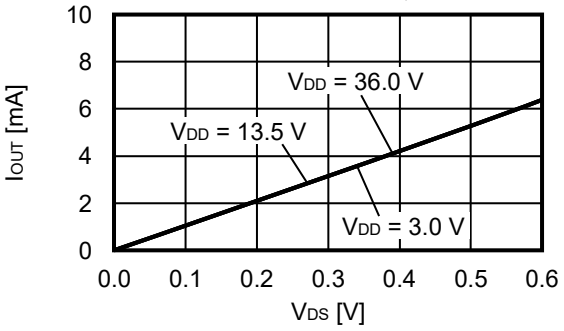
7. Nch transistor output current (I_{OUT}) vs. V_{DS}

7. 1 Undervoltage detection

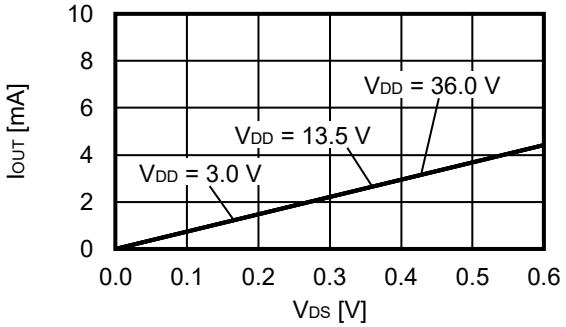
$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{SENSE} = 3.0 V, Ta = –40°C



$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{SENSE} = 3.0 V, Ta = +25°C

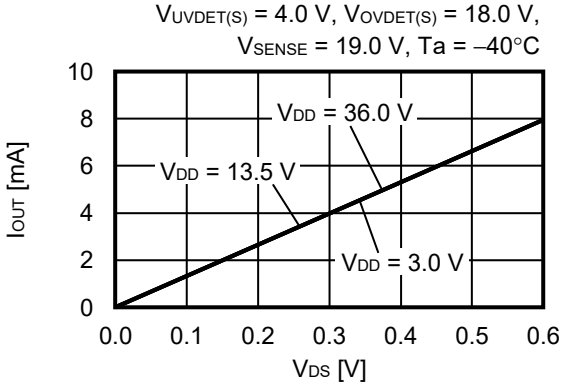


$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{SENSE} = 3.0 V, Ta = +125°C

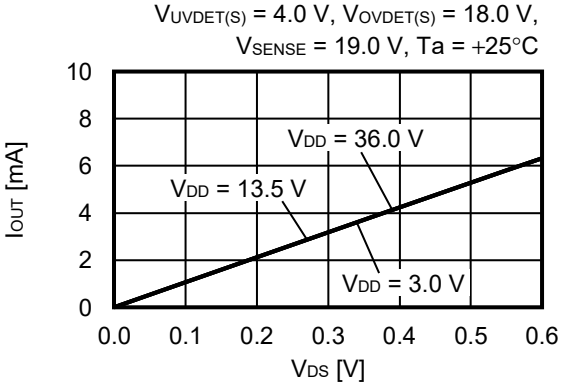


7. 2 Overvoltage detection

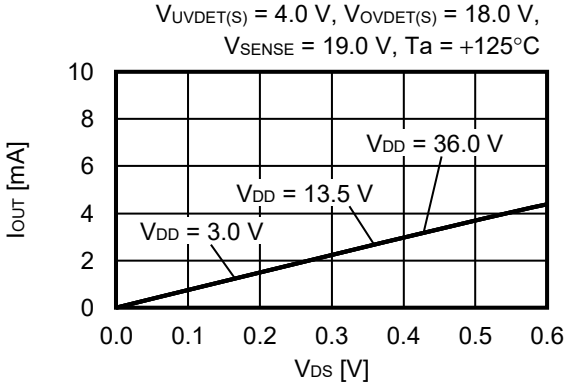
$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{SENSE} = 19.0 V, Ta = –40°C



$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{SENSE} = 19.0 V, Ta = +25°C



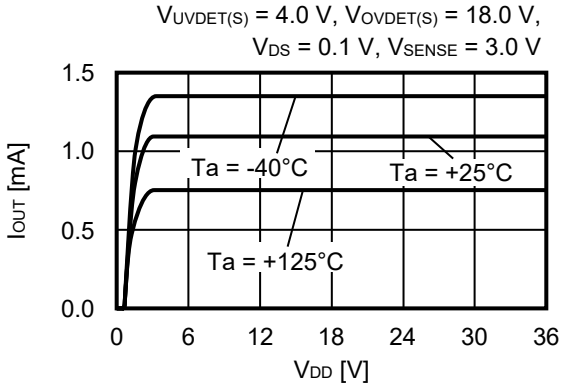
$V_{UVDET(S)}$ = 4.0 V, $V_{OVDET(S)}$ = 18.0 V,
V_{SENSE} = 19.0 V, Ta = +125°C



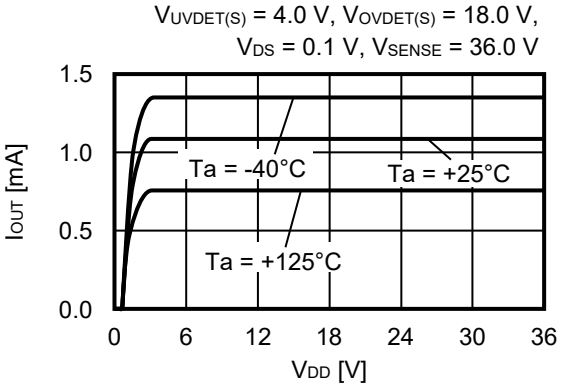
Remark V_{DS}: Drain-to-source voltage of the output transistor

8. Nch transistor output current (I_{OUT}) vs. Power supply voltage (V_{DD})

8. 1 Undervoltage detection



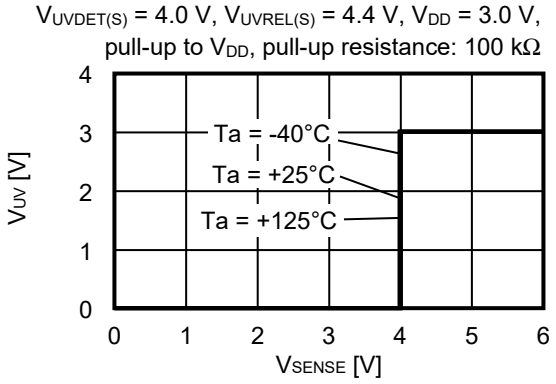
8. 2 Overvoltage detection

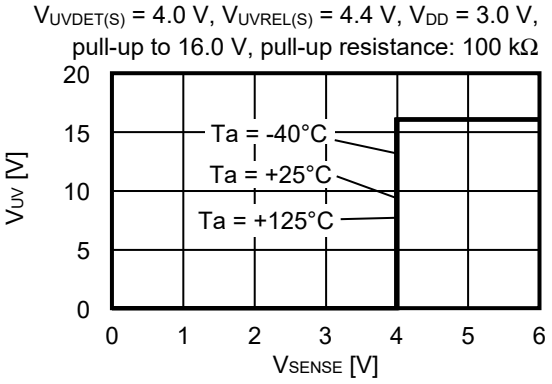


Remark V_{DS}: Drain-to-source voltage of the output transistor

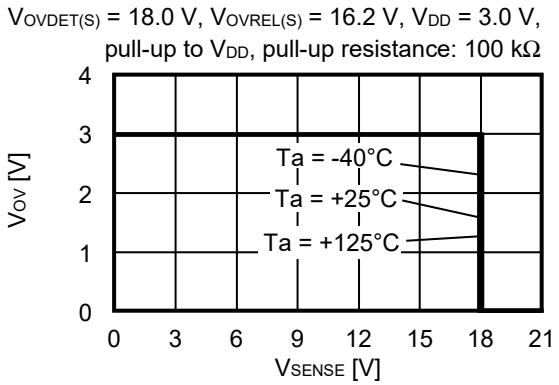
9. Output voltage (V_{UV}, V_{OV}) vs. SENSE pin voltage (V_{SENSE})

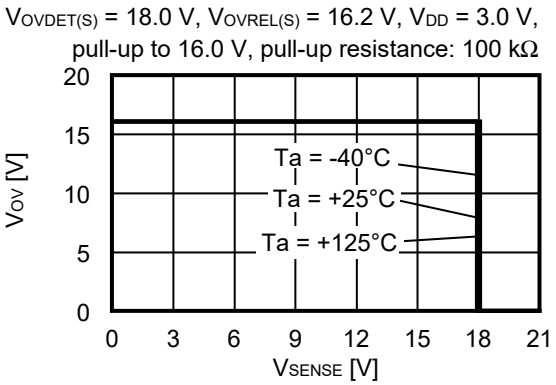
9. 1 Undervoltage detection





9. 2 Overvoltage detection

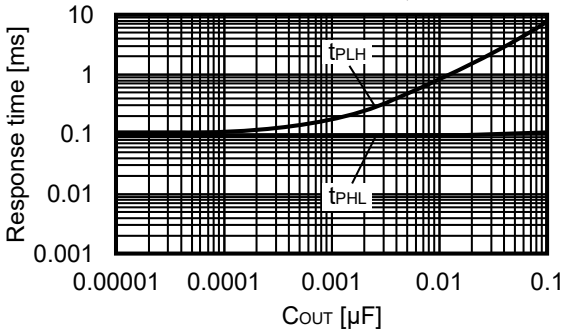




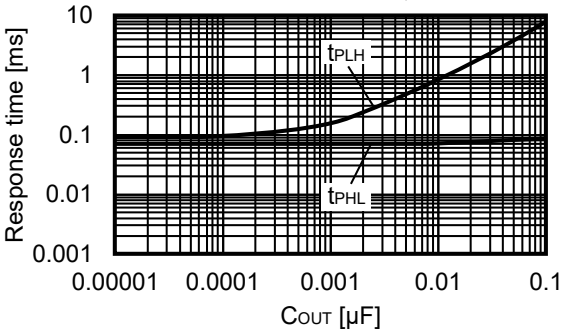
10. Dynamic response vs. Output pin capacitance (C_{OUT}) (CD pin; open)

10. 1 Undervoltage detection

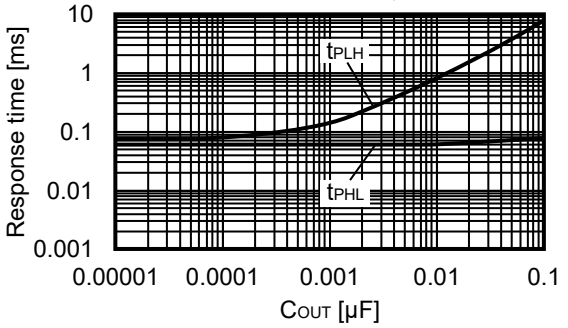
$V_{UVDET(S)}$ = 4.0 V, $V_{UVREL(S)}$ = 4.4 V,
V_{DD} = 13.5 V, Ta = –40°C



$V_{UVDET(S)}$ = 4.0 V, $V_{UVREL(S)}$ = 4.4 V,
V_{DD} = 13.5 V, Ta = +25°C

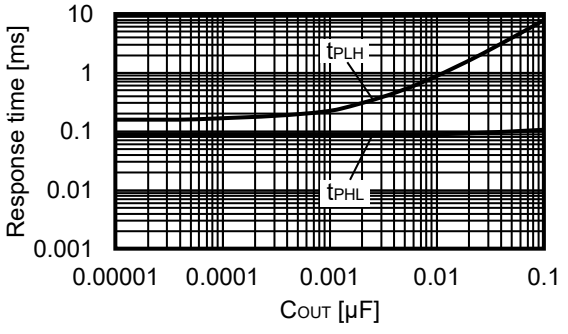


$V_{UVDET(S)}$ = 4.0 V, $V_{UVREL(S)}$ = 4.4 V,
V_{DD} = 13.5 V, Ta = +125°C

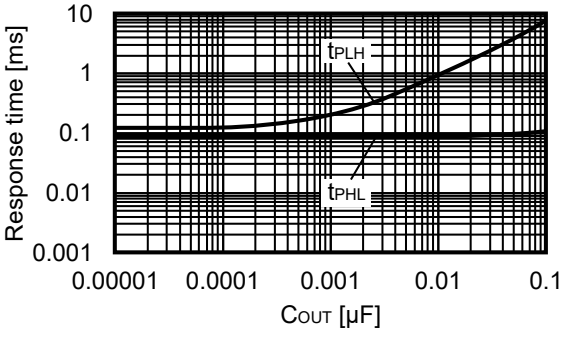


10. 2 Overvoltage detection

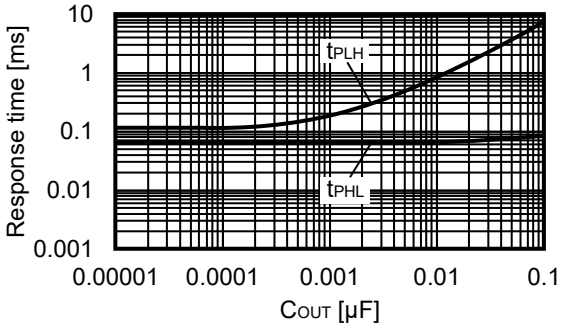
$V_{OVDET(S)}$ = 18.0 V, $V_{OVREL(S)}$ = 16.2 V,
V_{DD} = 13.5 V, Ta = –40°C

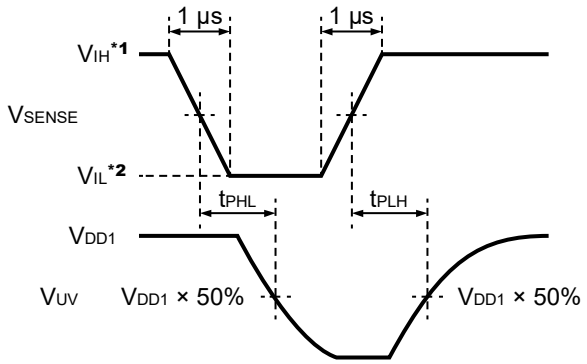


$V_{OVDET(S)}$ = 18.0 V, $V_{OVREL(S)}$ = 16.2 V,
V_{DD} = 13.5 V, Ta = +25°C



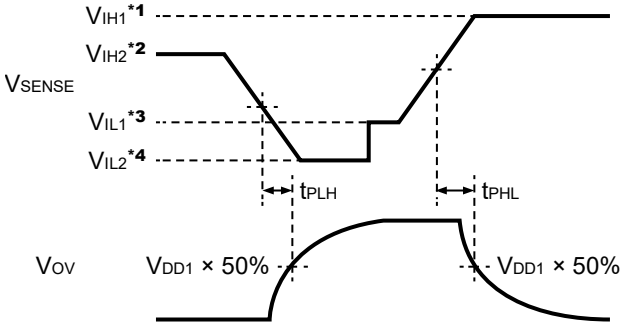
$V_{OVDET(S)}$ = 18.0 V, $V_{OVREL(S)}$ = 16.2 V,
V_{DD} = 13.5 V, Ta = +125°C





***1.** $V_{IH} = V_{UVDET(S)} + 1.0$ V
***2.** $V_{IL} = V_{UVDET(S)} - 1.0$ V

Figure 29 Test Condition of Response Time (Undervoltage Detection)



***1.** $V_{IH1} = V_{OVDET(S)} + 1.0$ V
***2.** $V_{IH2} = V_{OVREL(S)} + 1.0$ V
***3.** $V_{IL1} = V_{OVDET(S)} - 1.0$ V
***4.** $V_{IL2} = V_{OVREL(S)} - 1.0$ V

Figure 30 Test Condition of Response Time (Overvoltage Detection)

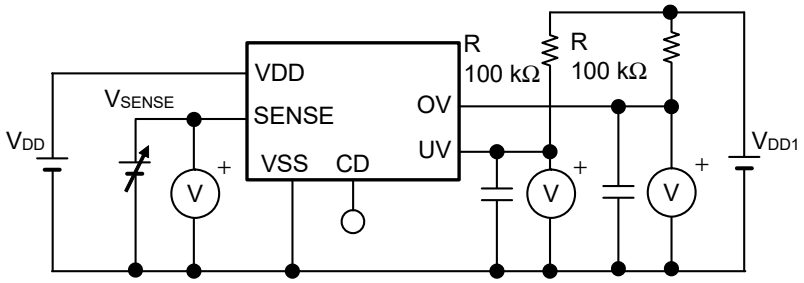


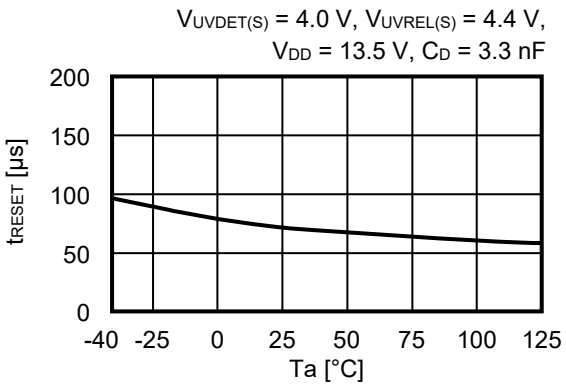
Figure 31 Test Circuit of Response Time

Caution 1. The above connection diagram and constants will not guarantee successful operation. Perform thorough evaluation including the temperature characteristics with an actual application to set the constants.
2. When the CD pin is open, a double pulse may appear at release.
To avoid the double pulse, attach 1 nF or more capacitor to the CD pin.

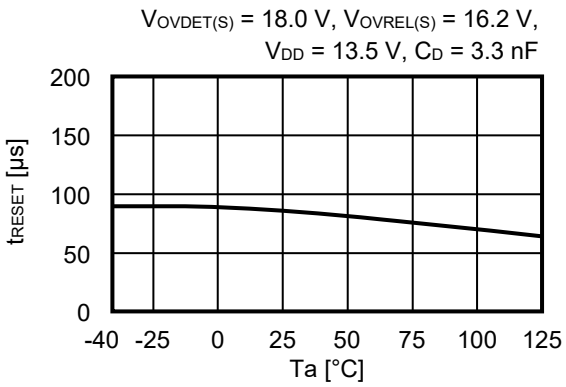
■ Reference Data

1. Detection response time (t_{RESET}) vs. Temperature (Ta)

1. 1 Undervoltage detection

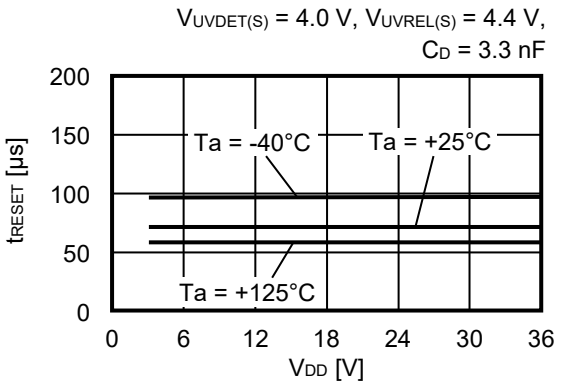


1. 2 Overvoltage detection

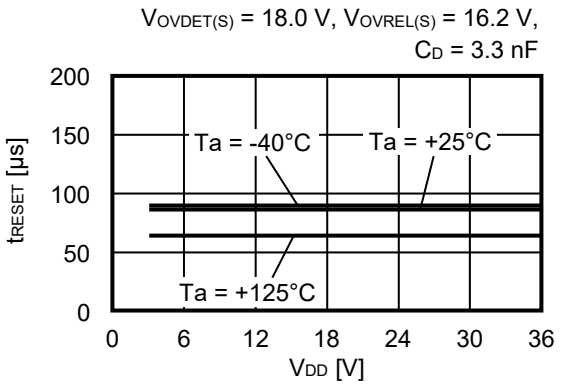


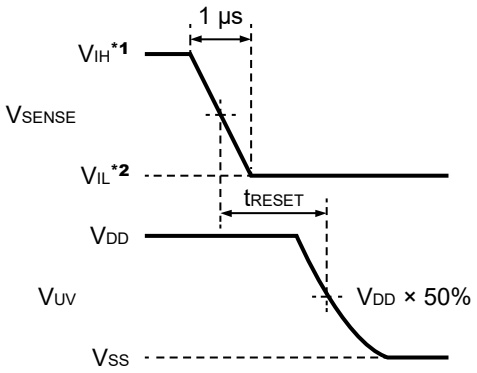
2. Detection response time (t_{RESET}) vs. Power supply voltage (V_{DD})

2. 1 Undervoltage detection



2. 2 Overvoltage detection





*1. $V_{IH} = V_{UVDET(S)} + 1.0$ V
*2. $V_{IL} = V_{UVDET(S)} - 1.0$ V

Figure 32 Test Condition of Detection Response Time (Undervoltage Detection)

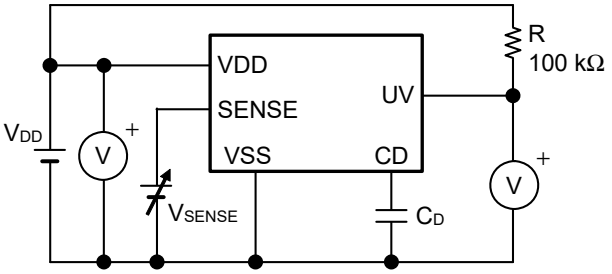
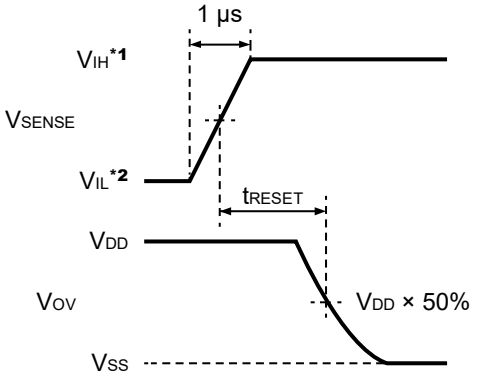


Figure 33 Test Circuit of Detection Response Time (Undervoltage Detection)



*1. $V_{IH} = V_{OVDET(S)} + 1.0$ V
*2. $V_{IL} = V_{OVDET(S)} - 1.0$ V

Figure 34 Test Condition of Detection Response Time (Overvoltage Detection)

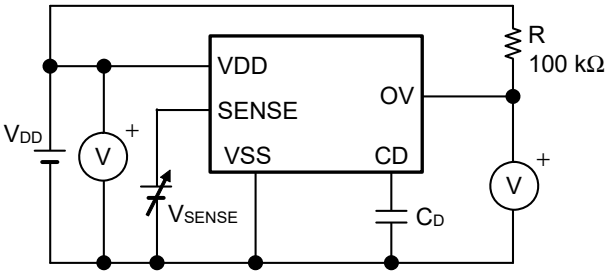
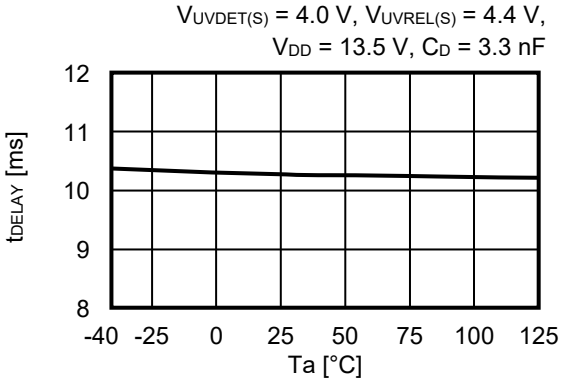


Figure 35 Test Circuit of Detection Response Time (Overvoltage Detection)

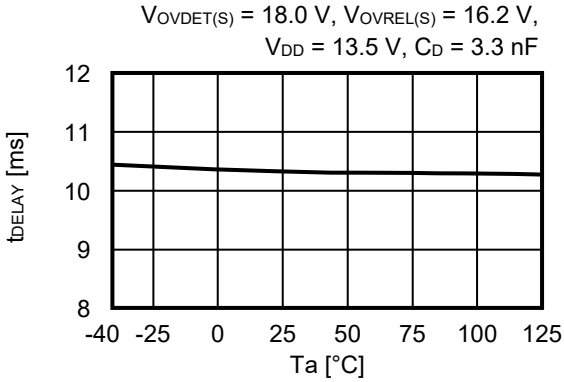
Caution The above connection diagram and constants will not guarantee successful operation. Perform thorough evaluation including the temperature characteristics with an actual application to set the constants.

3. Release delay time (t_{DELAY}) vs. Temperature (Ta)

3. 1 Undervoltage detection

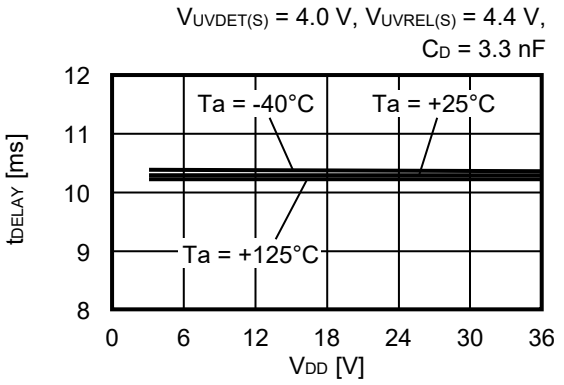


3. 2 Overvoltage detection

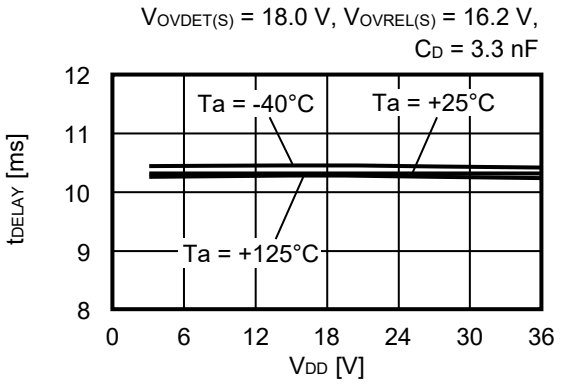


4. Release delay time (t_{DELAY}) vs. Power supply voltage (V_{DD})

4. 1 Undervoltage detection

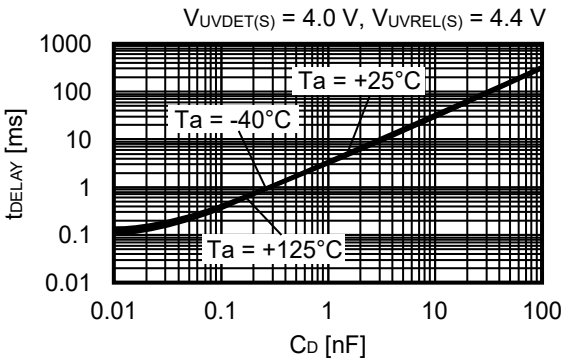


4. 2 Overvoltage detection

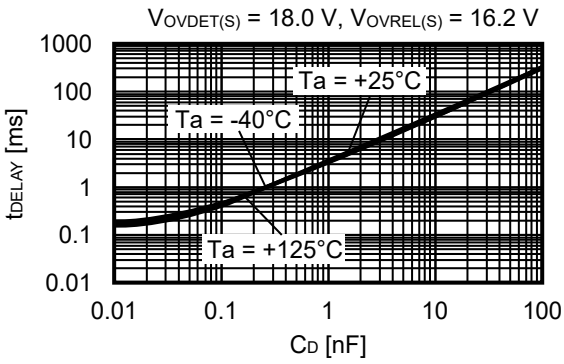


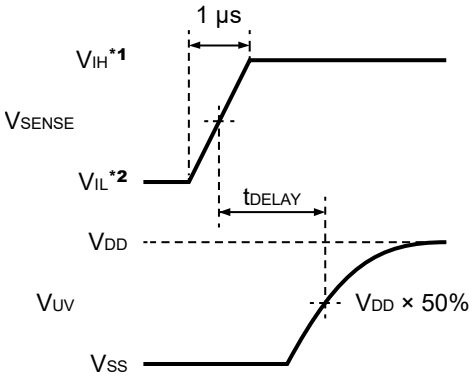
5. Release delay time (t_{DELAY}) vs. CD pin capacitance (C_D) (Without output pin capacitance)

5. 1 Undervoltage detection



5. 2 Overvoltage detection





*1. $V_{IH} = V_{UVREL(S)} + 1.0$ V
*2. $V_{IL} = V_{UVREL(S)} - 1.0$ V

Figure 36 Test Condition of Release Delay Time (Undervoltage Detection)

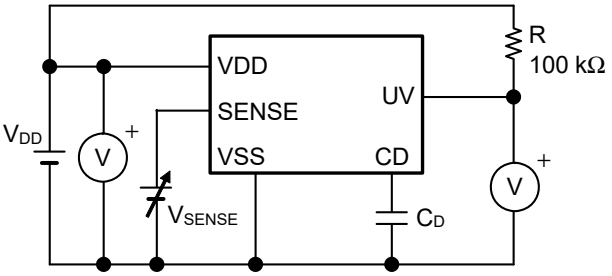
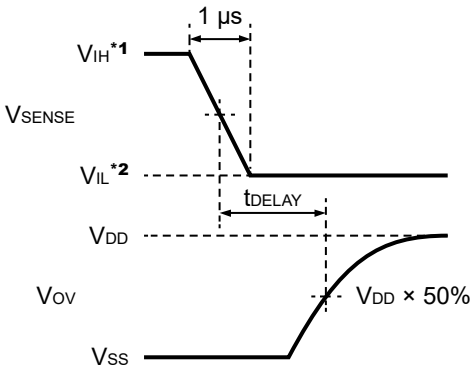


Figure 37 Test Circuit of Release Delay Time (Undervoltage Detection)



*1. $V_{IH} = V_{OVREL(S)} + 1.0$ V
*2. $V_{IL} = V_{OVREL(S)} - 1.0$ V

Figure 38 Test Condition of Release Delay Time (Overvoltage Detection)

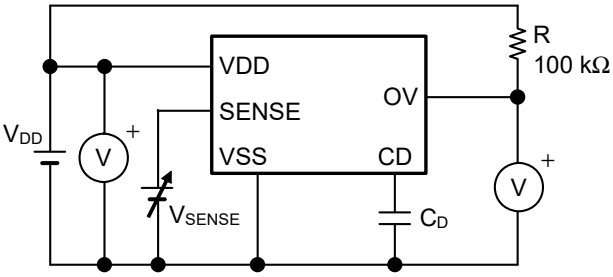
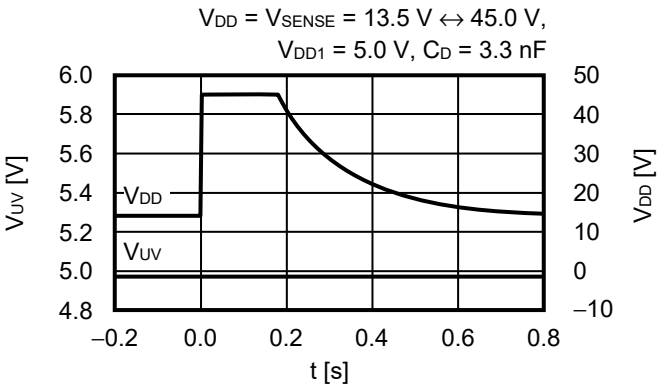


Figure 39 Test Circuit of Release Delay Time (Overvoltage Detection)

Caution The above connection diagram and constants will not guarantee successful operation. Perform thorough evaluation including the temperature characteristics with an actual application to set the constants.

6. Load dump characteristics (Ta = +25°C)

6. 1 $V_{UVDET(S)}$ = 4.0 V



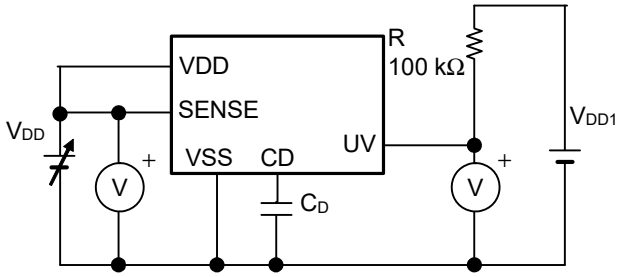
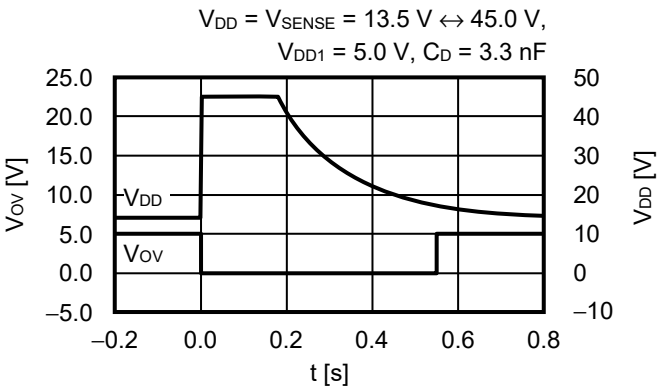


Figure 40

6. 2 $V_{OVDET(S)}$ = 18.0 V



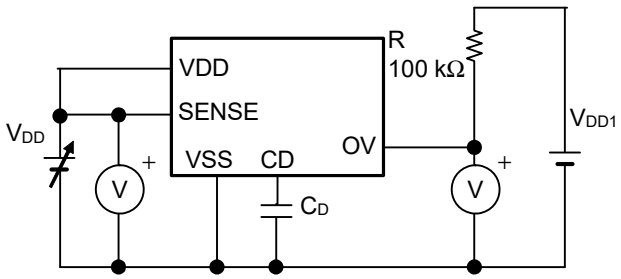
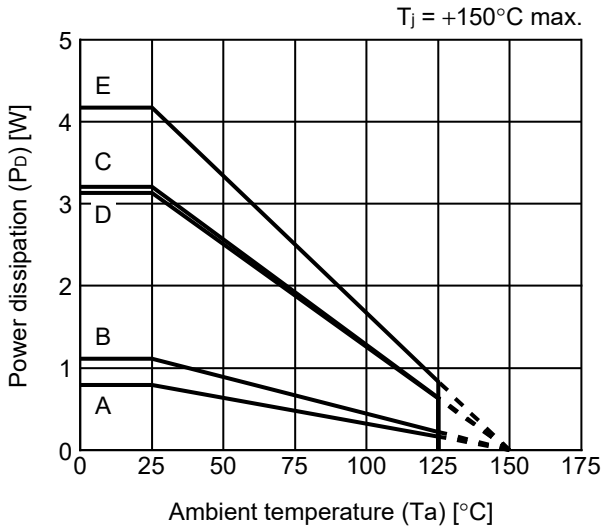


Figure 41

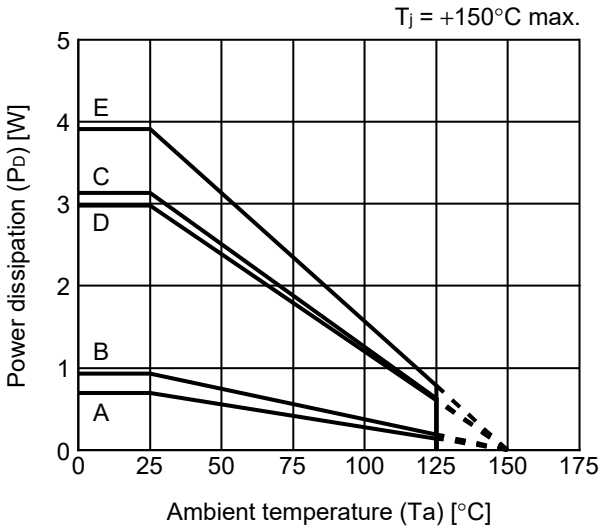
■ Power Dissipation

HTMSOP-8



Board	Power Dissipation (P_D)
A	0.79 W
B	1.11 W
C	3.21 W
D	3.13 W
E	4.17 W

HSNT-8(2030)

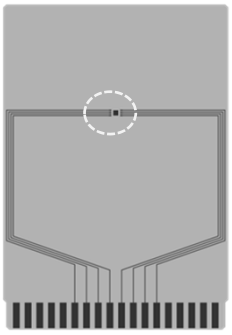


Board	Power Dissipation (P_D)
A	0.69 W
B	0.93 W
C	3.13 W
D	2.98 W
E	3.91 W

HTMSOP-8 Test Board

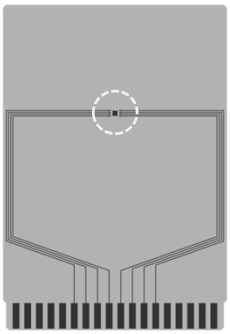
IC Mount Area

(1) Board A



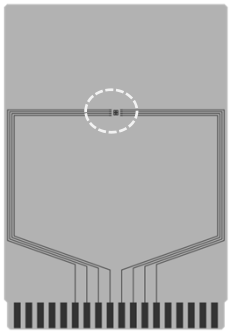
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

(3) Board C



enlarged view

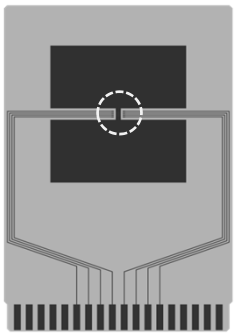
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm

No. HTMSOP8-A-Board-SD-1.0

HTMSOP-8 Test Board

IC Mount Area

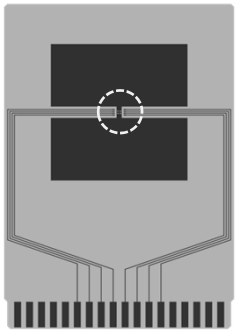
(4) Board D



enlarged view

Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Pattern for heat radiation: 2000mm^2 t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

(5) Board E



enlarged view

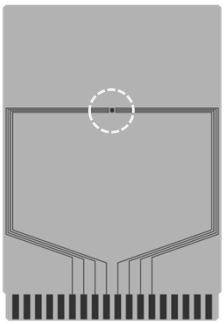
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Pattern for heat radiation: 2000mm^2 t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm

No. HTMSOP8-A-Board-SD-1.0

HSNT-8(2030) Test Board

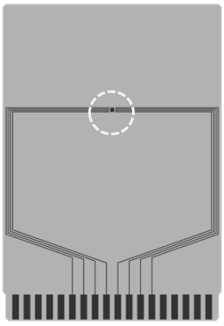
IC Mount Area

(1) Board A



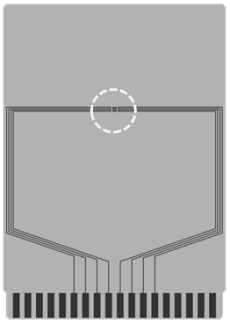
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

(3) Board C



enlarged view

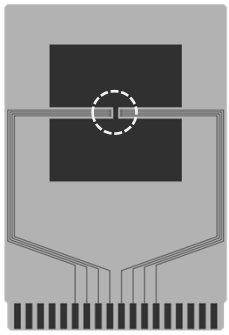
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm

No. HSNT8-A-Board-SD-2.0

HSNT-8(2030) Test Board

IC Mount Area

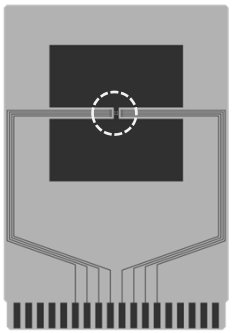
(4) Board D



enlarged view

Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Pattern for heat radiation: 2000mm^2 t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

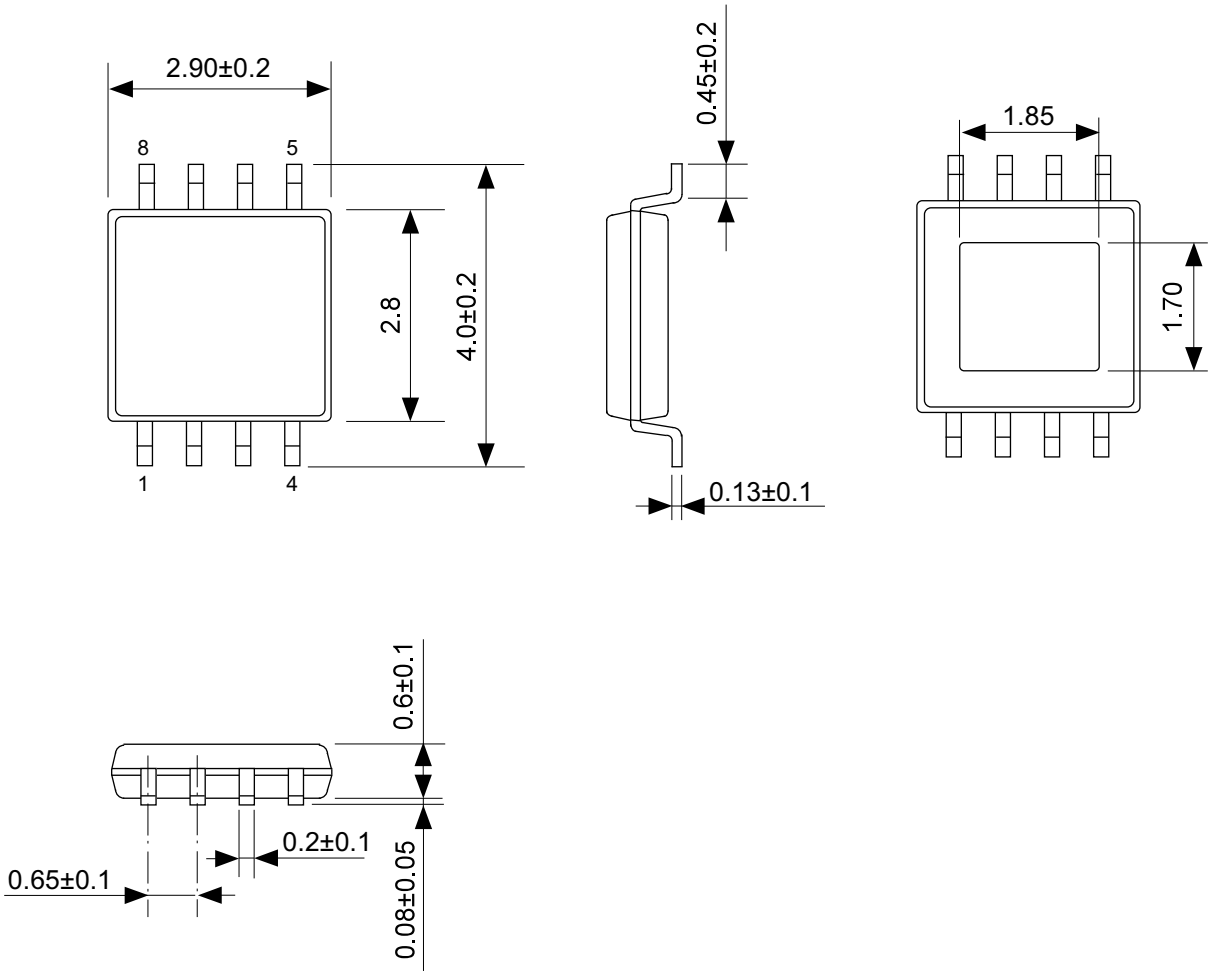
(5) Board E



enlarged view

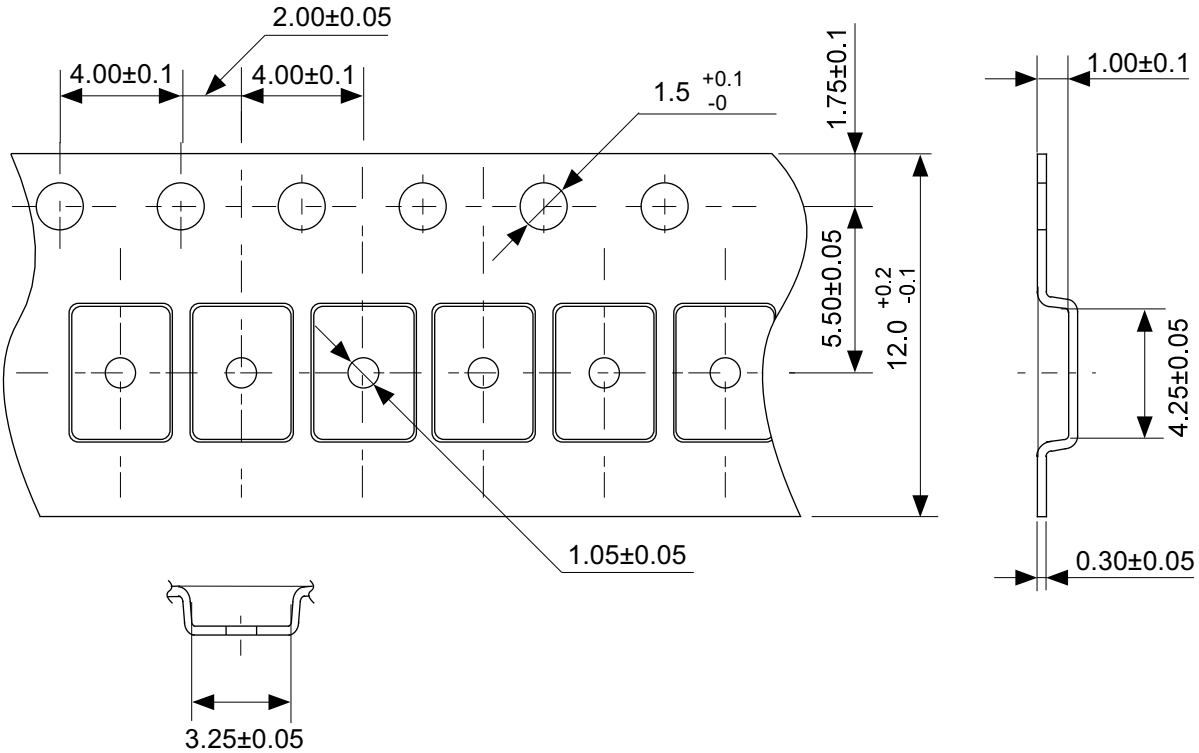
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Pattern for heat radiation: 2000mm^2 t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm

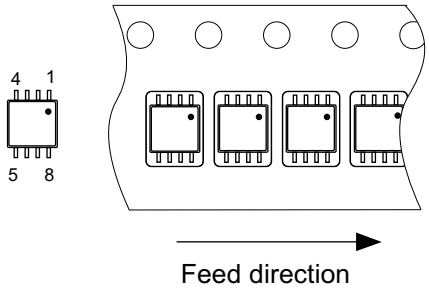
No. HSNT8-A-Board-SD-2.0



No. FP008-A-P-SD-2.0

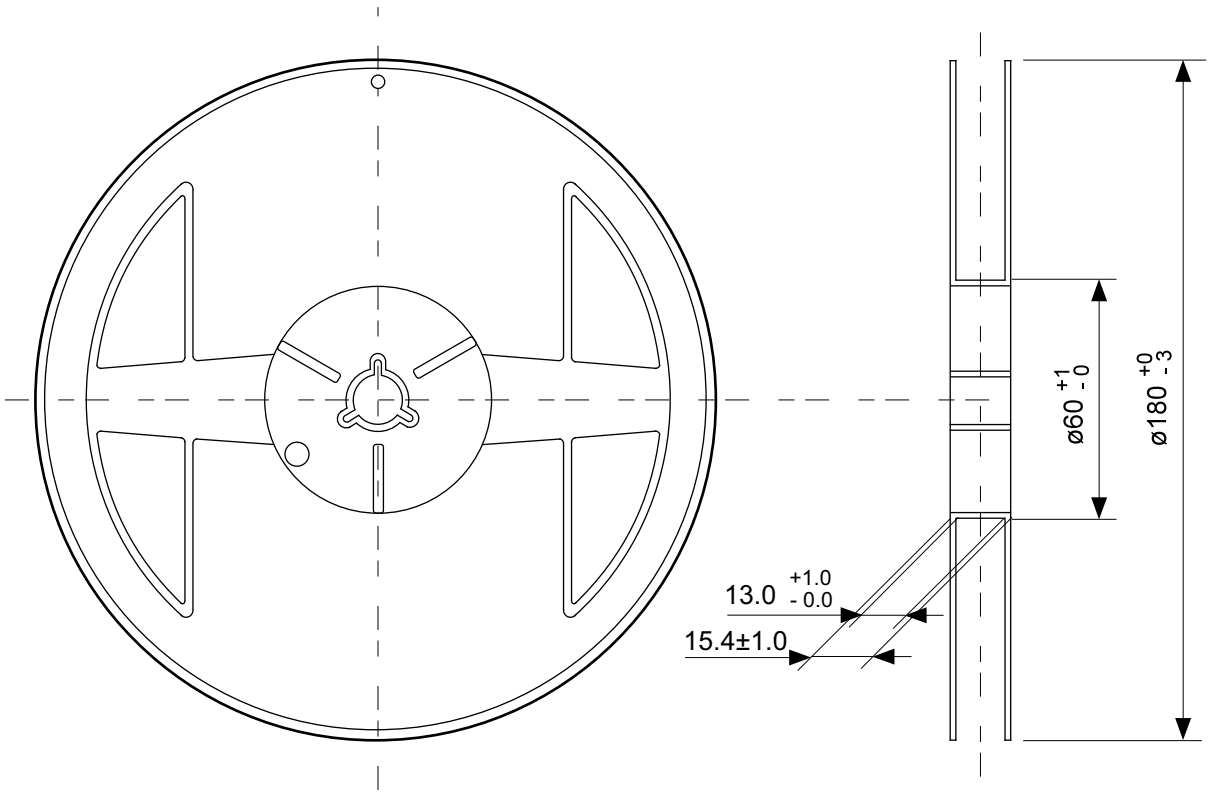
TITLE	HTMSOP8-A-PKG Dimensions
No.	FP008-A-P-SD-2.0
ANGLE	
UNIT	mm
ABLIC Inc.	



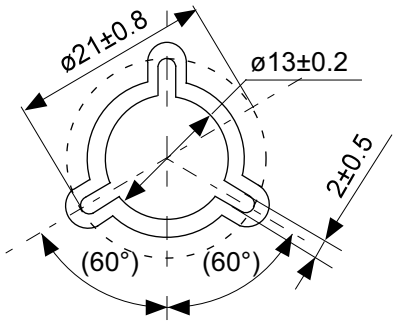


No. FP008-A-C-SD-1.0

TITLE	HTMSOP8-A-Carrier Tape
No.	FP008-A-C-SD-1.0
ANGLE	
UNIT	mm
ABLIC Inc.	

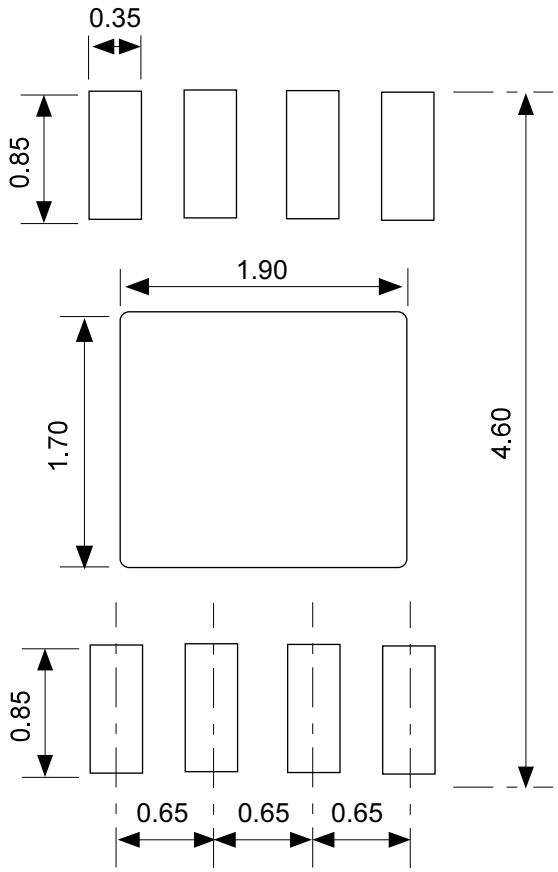


Enlarged drawing in the central part



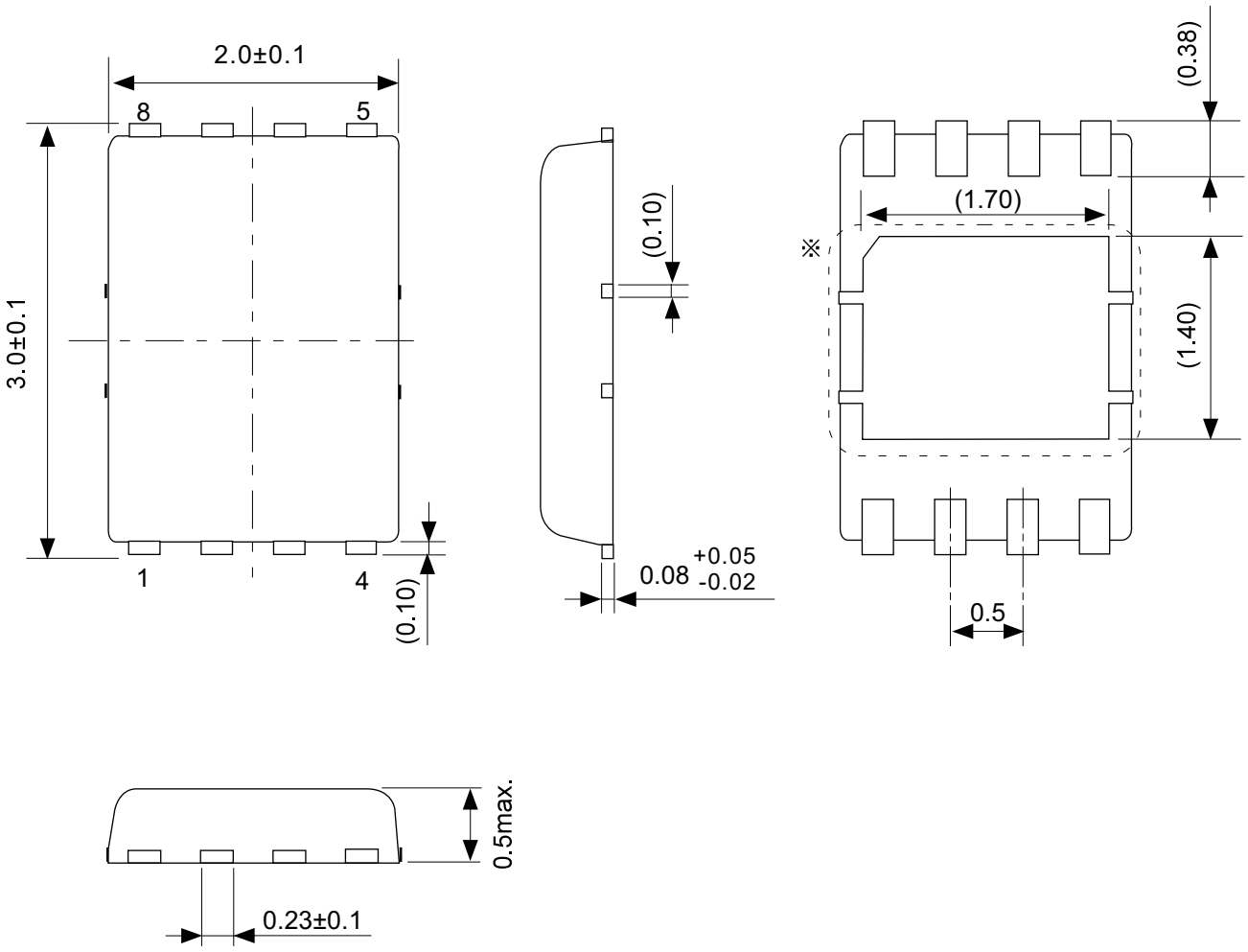
No. FP008-A-R-SD-2.0

TITLE	HTMSOP8-A-Reel		
No.	FP008-A-R-SD-2.0		
ANGLE		QTY.	4,000
UNIT	mm		
ABLIC Inc.			



No. FP008-A-L-SD-2.0

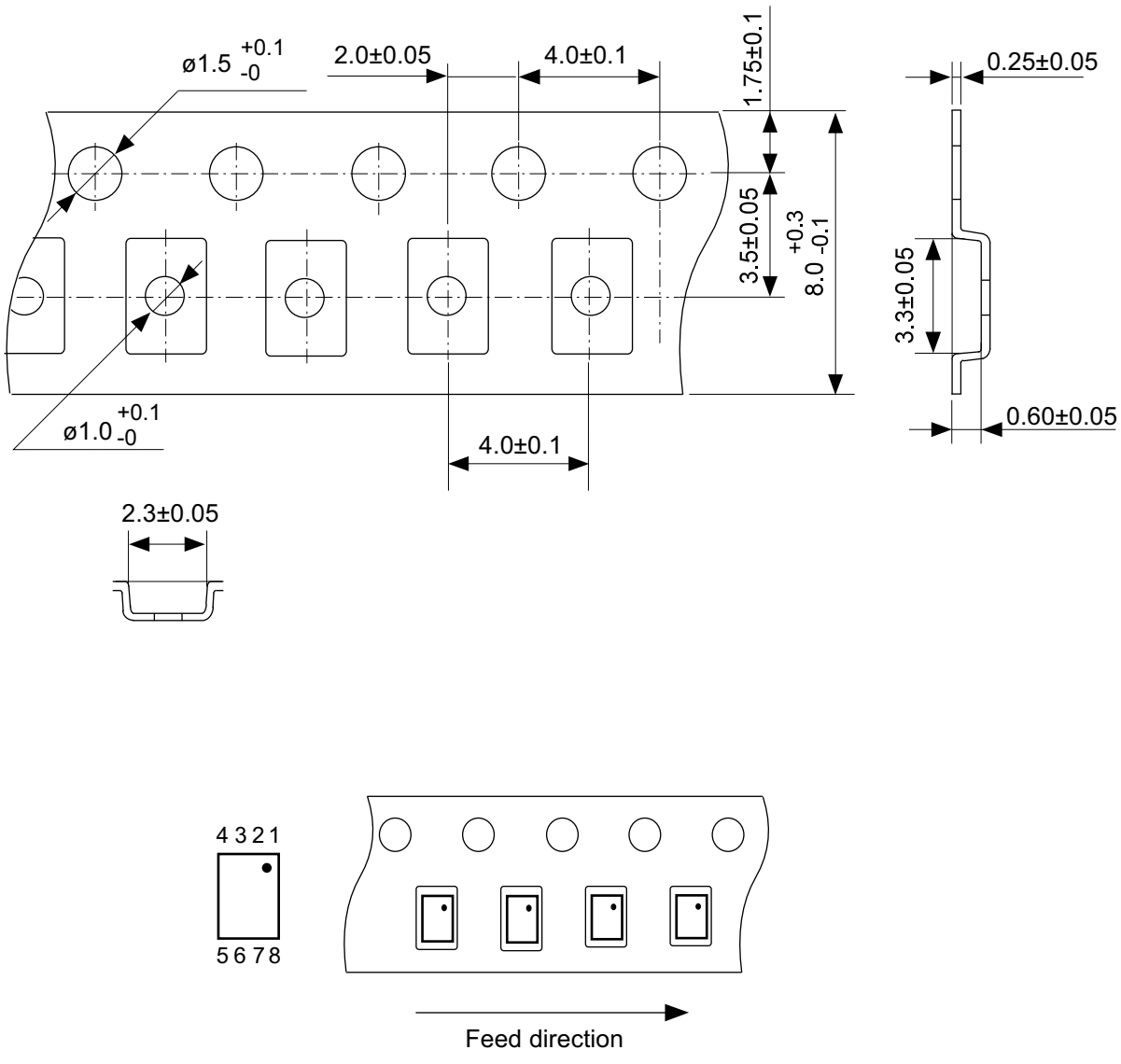
TITLE	HTMSOP8-A -Land Recommendation
No.	FP008-A-L-SD-2.0
ANGLE	
UNIT	mm
ABLIC Inc.	



※ The heat sink of back side has different electric potential depending on the product.
Confirm specifications of each product.
Do not use it as the function of electrode.

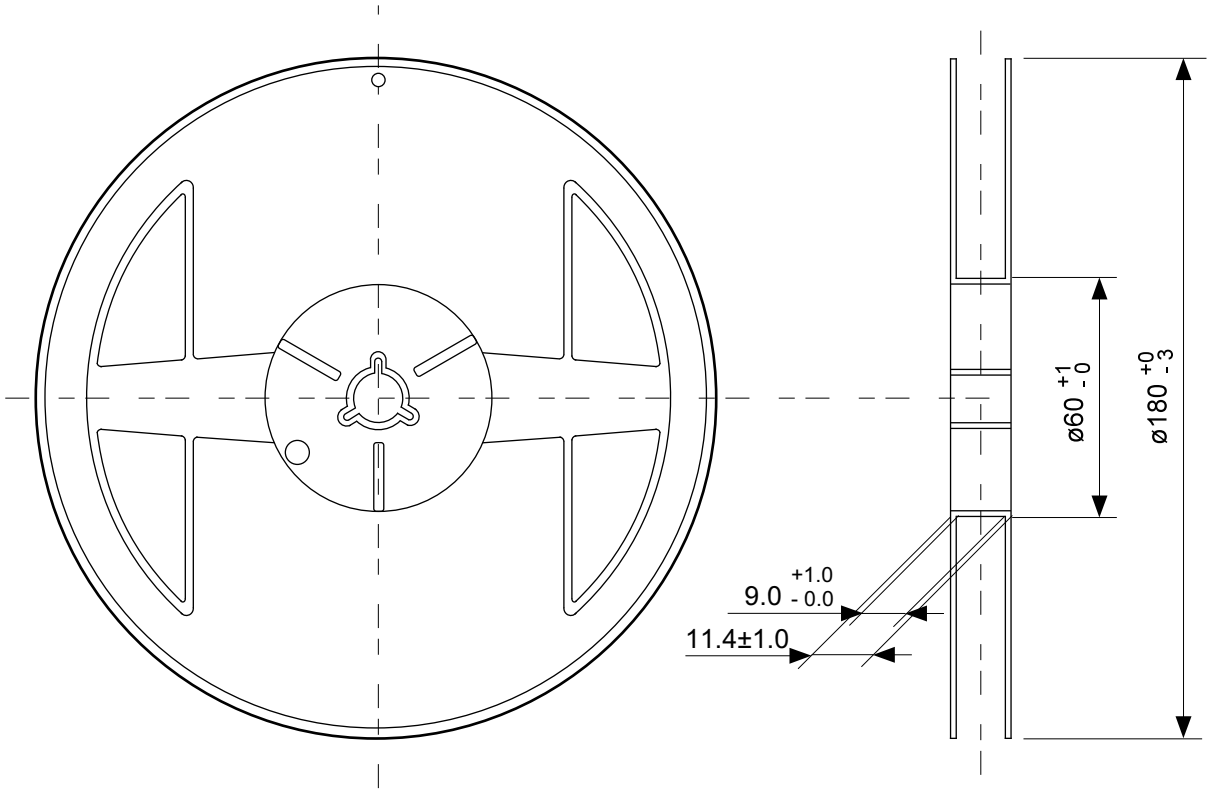
No. PP008-A-P-SD-2.0

TITLE	HSNT-8-A-PKG Dimensions
No.	PP008-A-P-SD-2.0
ANGLE	
UNIT	mm
ABLIC Inc.	

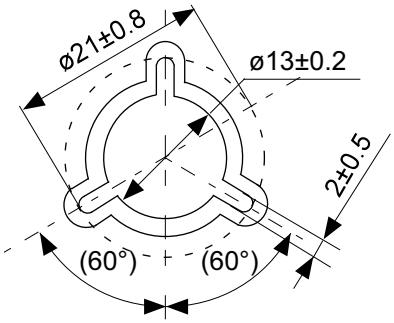


No. PP008-A-C-SD-1.0

TITLE	HSNT-8-A-Carrier Tape
No.	PP008-A-C-SD-1.0
ANGLE	
UNIT	mm
ABLIC Inc.	

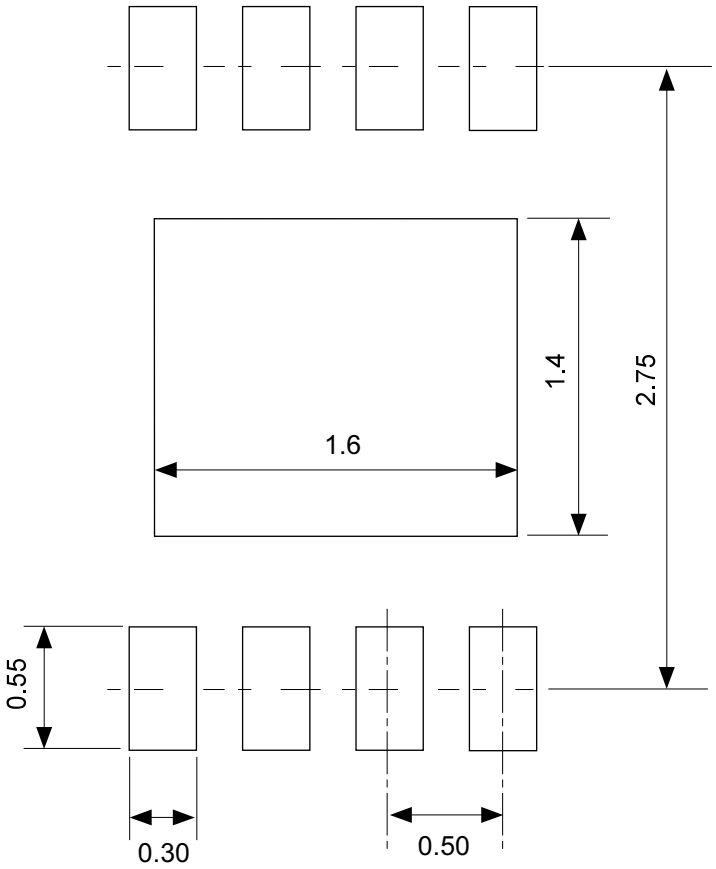


Enlarged drawing in the central part



No. PP008-A-R-SD-2.0

TITLE	HSNT-8-A-Reel		
No.	PP008-A-R-SD-2.0		
ANGLE		QTY.	5,000
UNIT	mm		
ABLIC Inc.			



No. PP008-A-L-SD-1.0

TITLE	HSNT-8-A -Land Recommendation
No.	PP008-A-L-SD-1.0
ANGLE	
UNIT	mm
ABLIC Inc.	

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